

EMI-RFI Considerations in Precision Linear Circuits

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Precision Analog – Linear products*

*EMIRR content based on work by
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and
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Precision Analog – Linear Products*

EMI-RFI

first things first

- TI's interest in EMI-RFI is simply one of providing assistance to our customers who must prevent or resolve EMI-RFI issues affecting the performance of our products in their circuit application
- I would like to acknowledge the contributions of some of the people who have provided industry a wealth of information about EMI-RFI
 - *The Designers Guide to Electromagnetic Compatibility, EDN -William D. Kimmel, PE, and Daryl D. Gerke, PE, - Kimmel Gerke Associates, Ltd*
 - *Electromagnetic Compatibility Engineering – A Wiley and Sons Publication - Henry W. Ott – Henry Ott Consultants*
 - *Audio Systems Group, Inc. – Jim Brown*

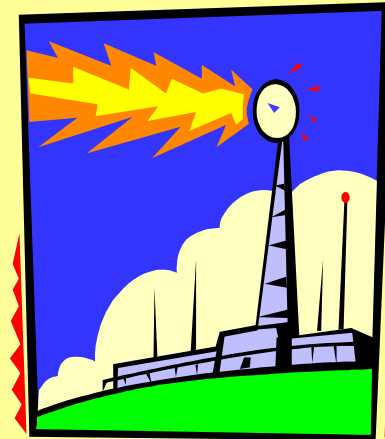
EMI–RFI

EMI – Electromagnetic Interference

RFI – Radio frequency Interference

Why are EMI and RFI a concern?

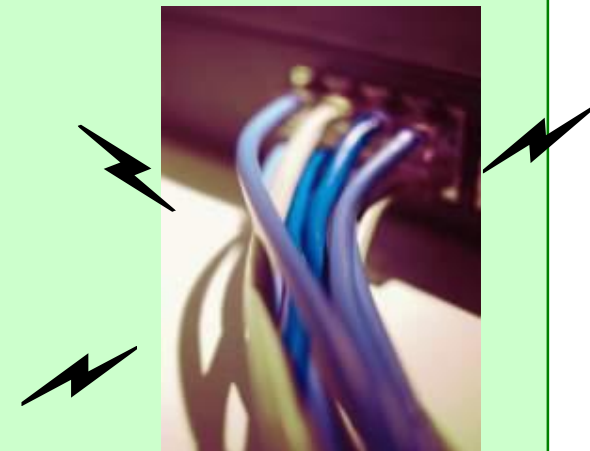
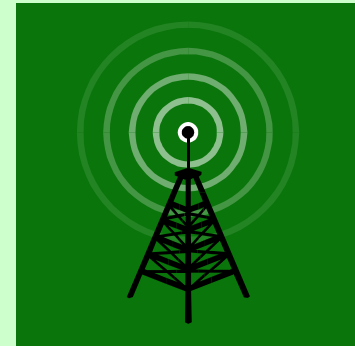
- Radio spectrum pollution
- Compatibility within circuits
- System disturbance, malfunction or possibly damage
- Regulatory conformance



EMI or RFI?

Both are sources of radio frequency (RF) disturbance

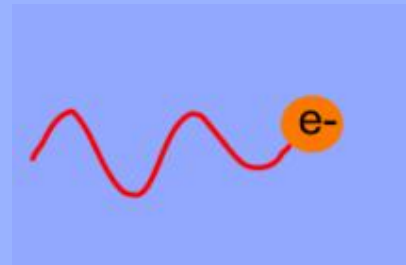
- RFI – radio frequency interference
 - Often a narrowband RF source
 - RF is often intentionally radiated
- EMI – electromagnetic interference
 - Often a broadband RF source
 - RF is often unintentionally radiated
- Terms are often used interchangeably



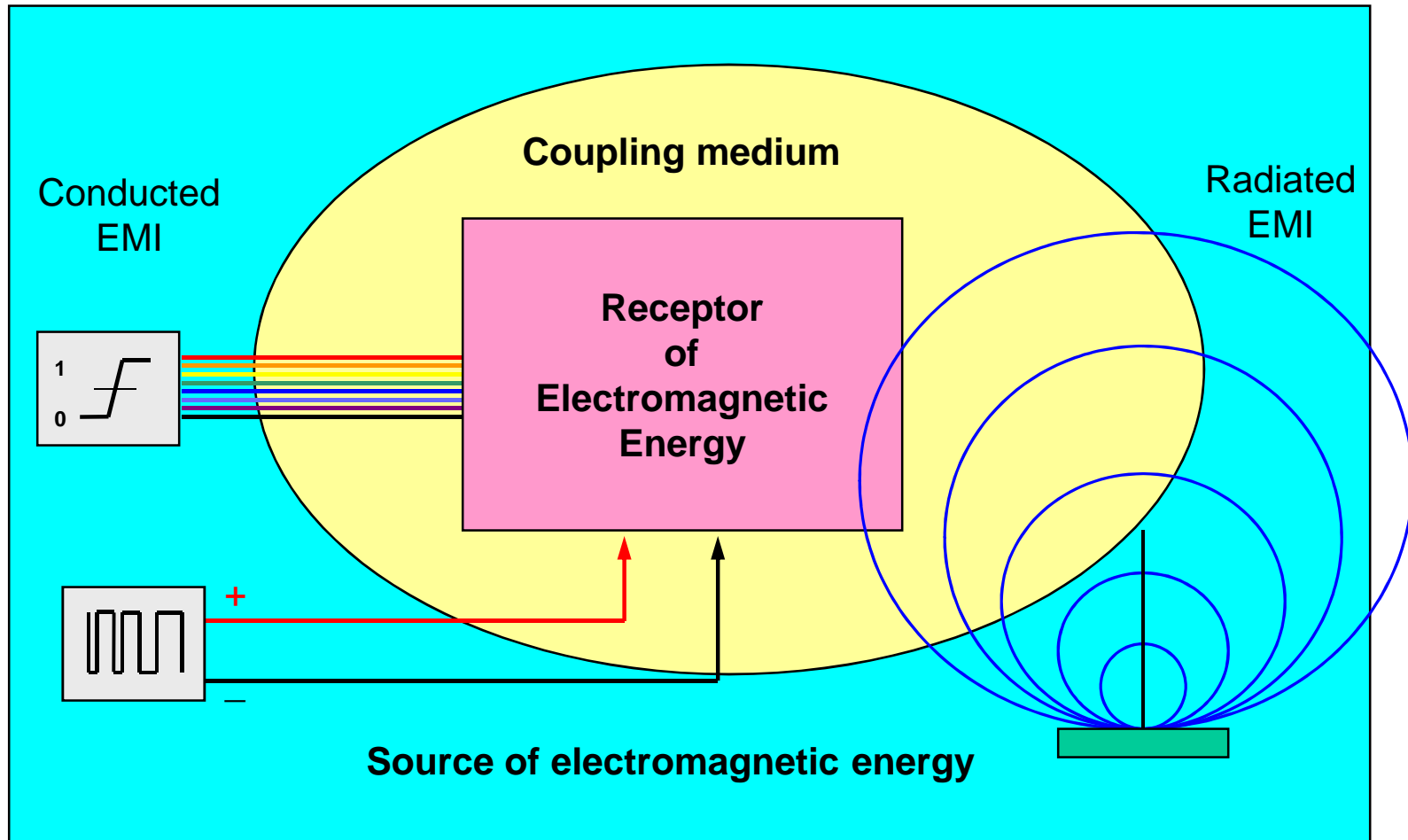
EMI can propagate by one or more types of fields

- Electric Field (E) – Force created by uneven charge distribution
- Magnetic Induction Field (H) – Force created by moving charges
- Electromagnetic Field – Created whenever charges are accelerated

Source http://www.w8ji.com/radiation_and_fields.htm

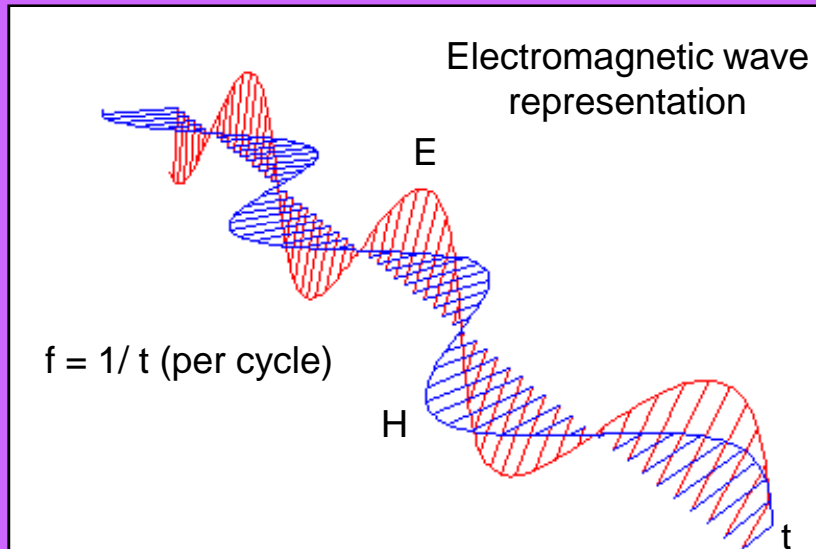


The necessary elements for EMI



Radiated EMI will be converted to conducted EMI when it is intercepted by conductors!

Sources of electromagnetic energy



RF generating sources

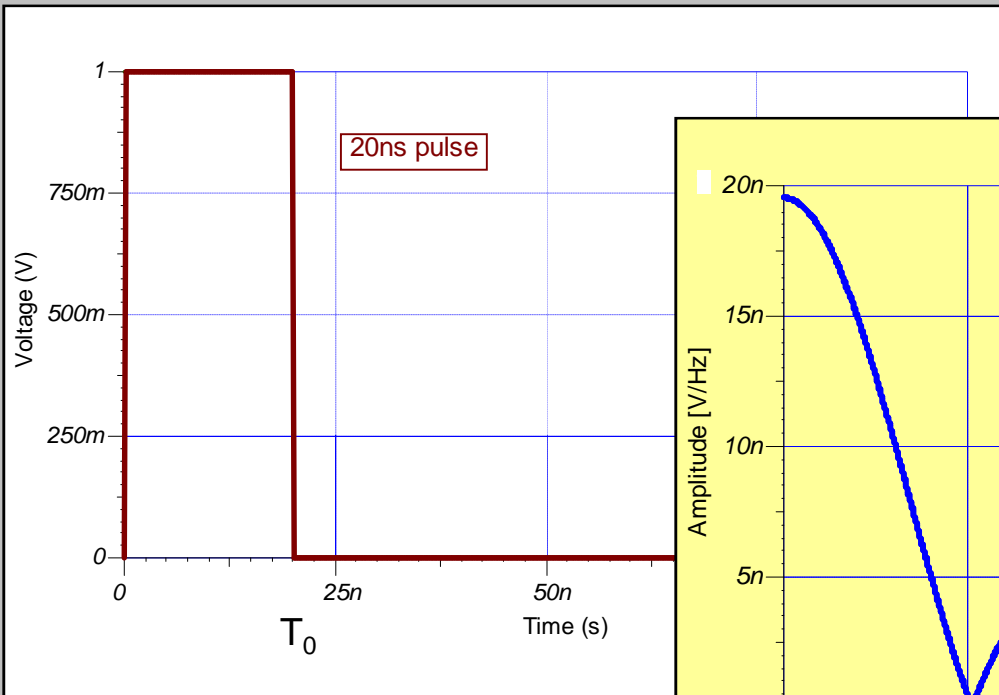
Intentional radiators

- Cell phones & personal electronics
- Transmitters & transceivers
- Wireless routers, peripherals
- Wireless instrumentation

Unintentional radiators

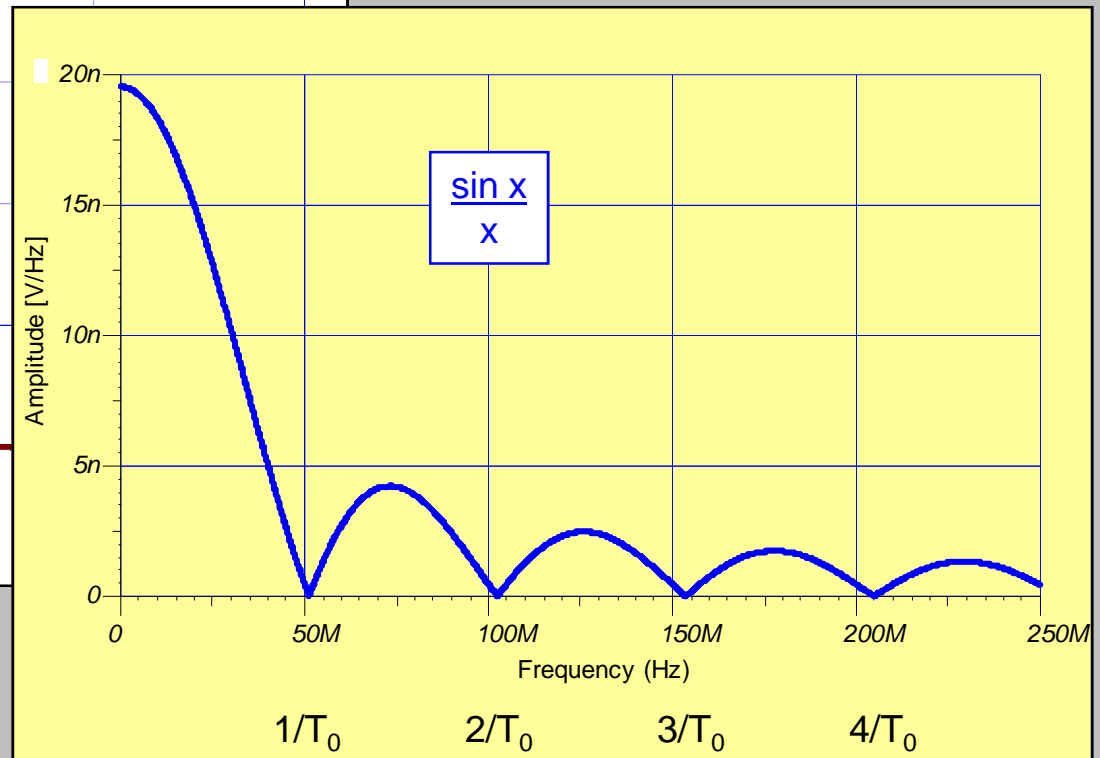
- System clocks & oscillators
- Processors & logic circuits
- Switching power supplies
- Switching amplifiers
- Electromechanical devices
- Electrical power line services

How radio frequency energy comes about in circuits



$$|X(f)| = \sqrt{\text{Re}(f)^2 + \text{Im}(f)^2}$$

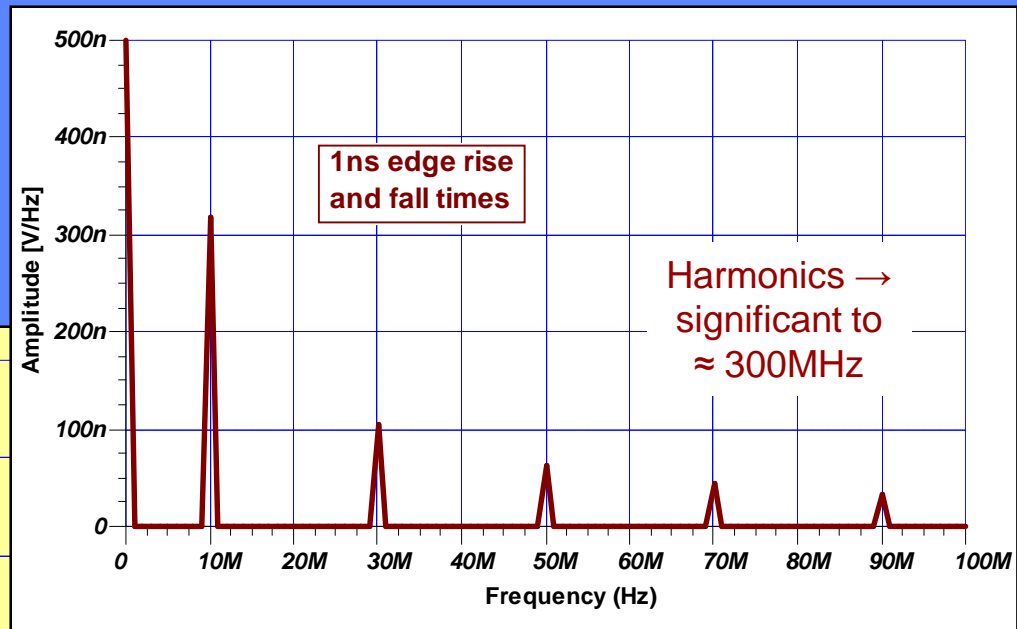
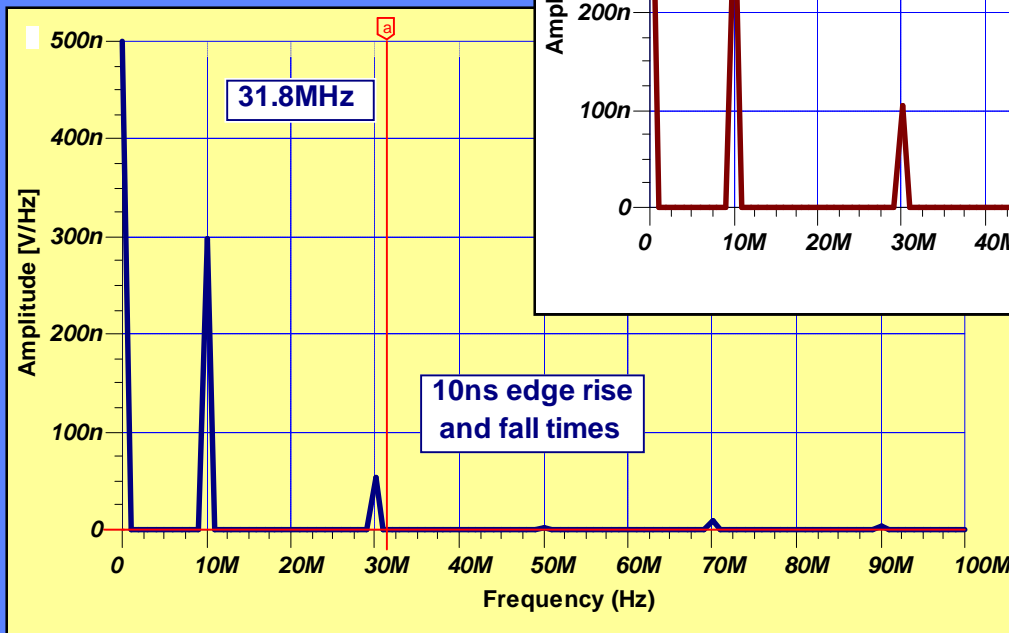
Complex frequency domain in
Polar form



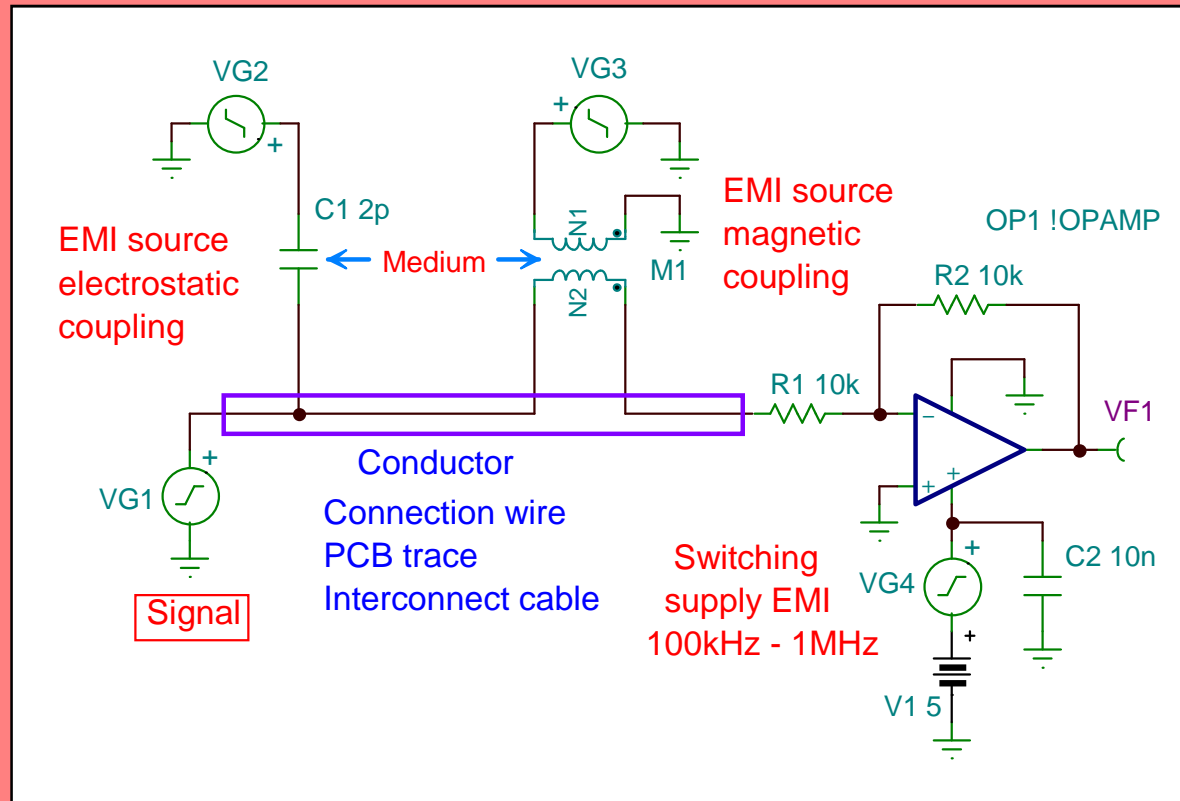
It's about edge rates

A rule of thumb for digital signals and transients

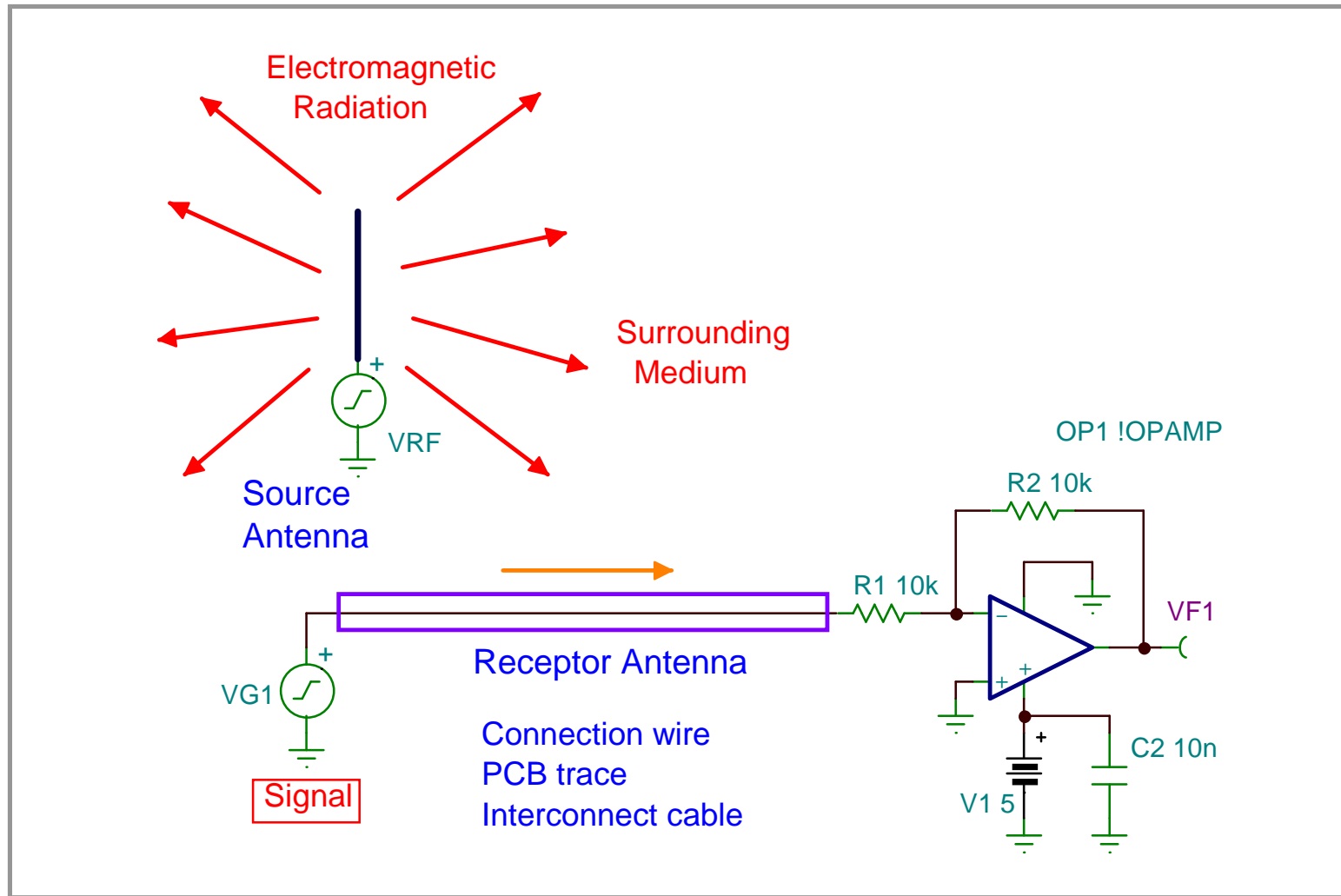
$$f_{\max} = (p * t_{\text{rise}})^{-1}$$



The coupling medium for conducted emissions



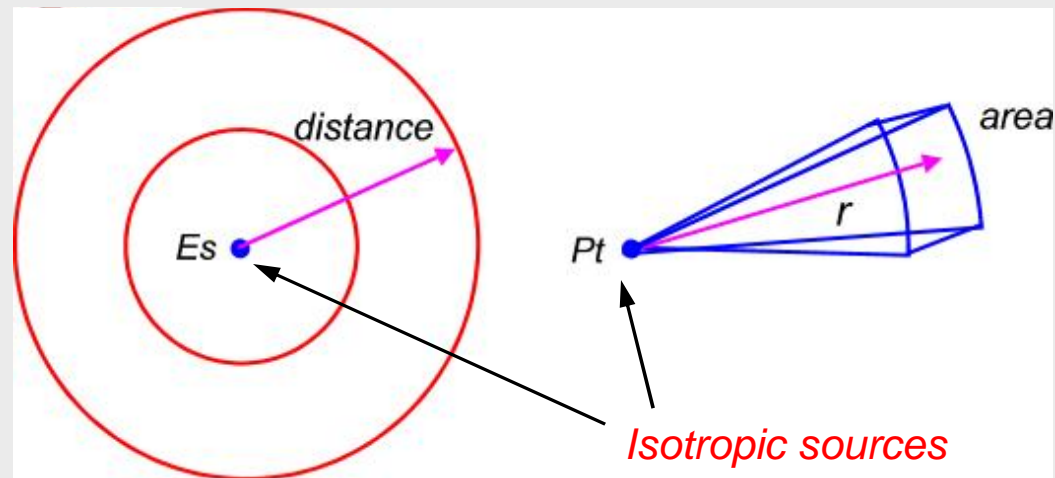
The coupling medium for radiated emissions



Electric-field strength and power density

EMI - electric-field strength units

Communications - power density units



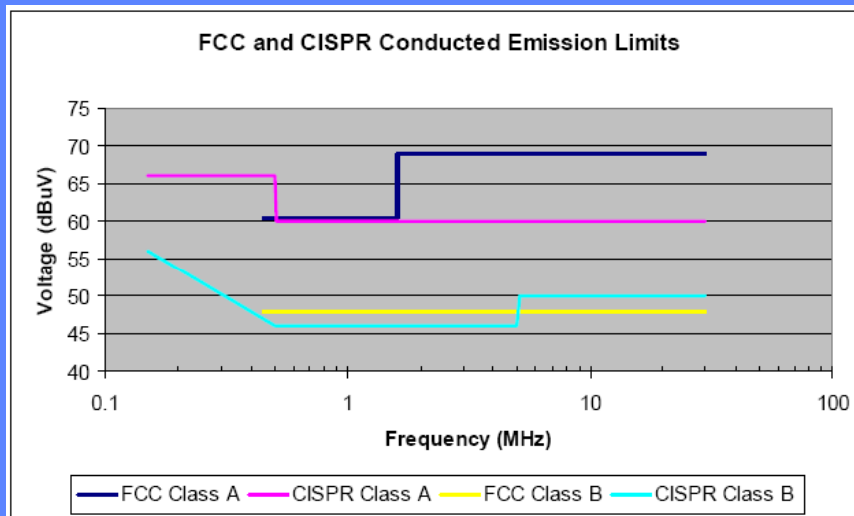
$$E \text{ (V/m)} = 61.4 [P(\text{mW}) / \text{cm}^2]^{1/2}$$

$$P_d = P_t / 4\pi \cdot r^2 \quad (\text{W/m}^2 \text{ or mW/cm}^2)$$

| | |
|---------------------------------|--------------------------------|
| 100V/m = 2.65mW/cm ² | 10mW/cm ² = 194V/m |
| 10V/m = 26uW/cm ² | 1mW/cm ² = 61V/m |
| 1V/m = 0.26uW/cm ² | 0.1mW/cm ² = 1.9V/m |

Emission source limits

Conducted Emissions - 10kHz to 30MHz

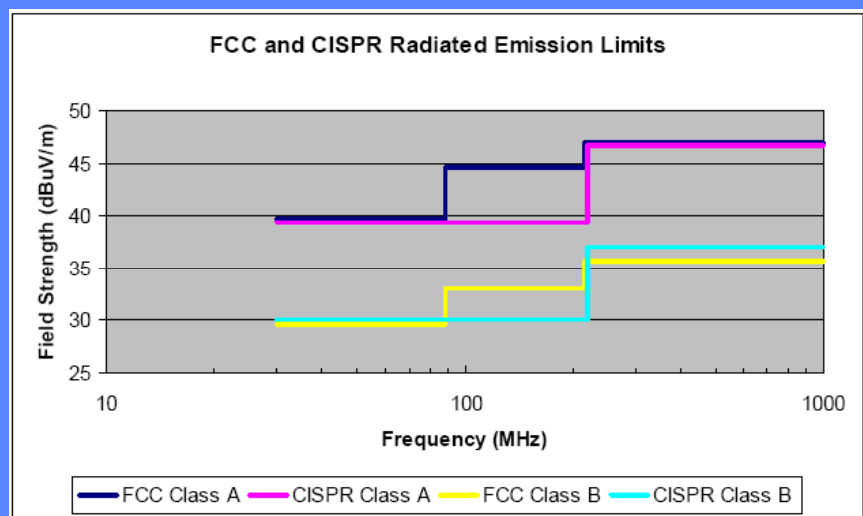


| Freq (MHz) | Class A dBuV | Class B dBuV |
|------------|--------------|--------------|
| 0.45 - 1.6 | 60 | 48 |
| 1.6 - 30 | 69.5 | 48 |

Sources: SynQor app. note 00-08-02 Rev. 04
& www.cclab.com/engnotes/eng290.htm

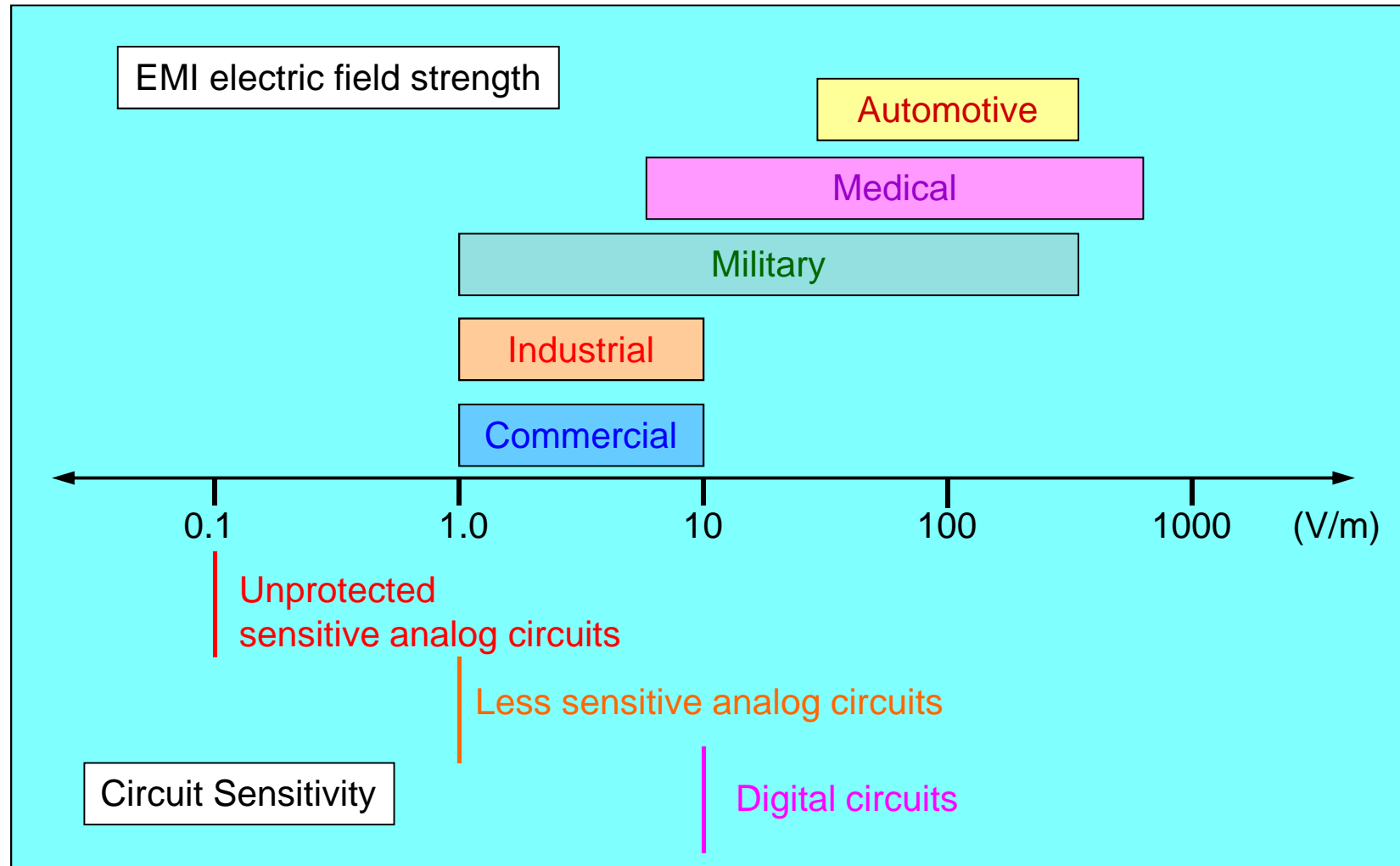
Radiated Emissions - 30MHz to 1GHz

measurement distance 10m

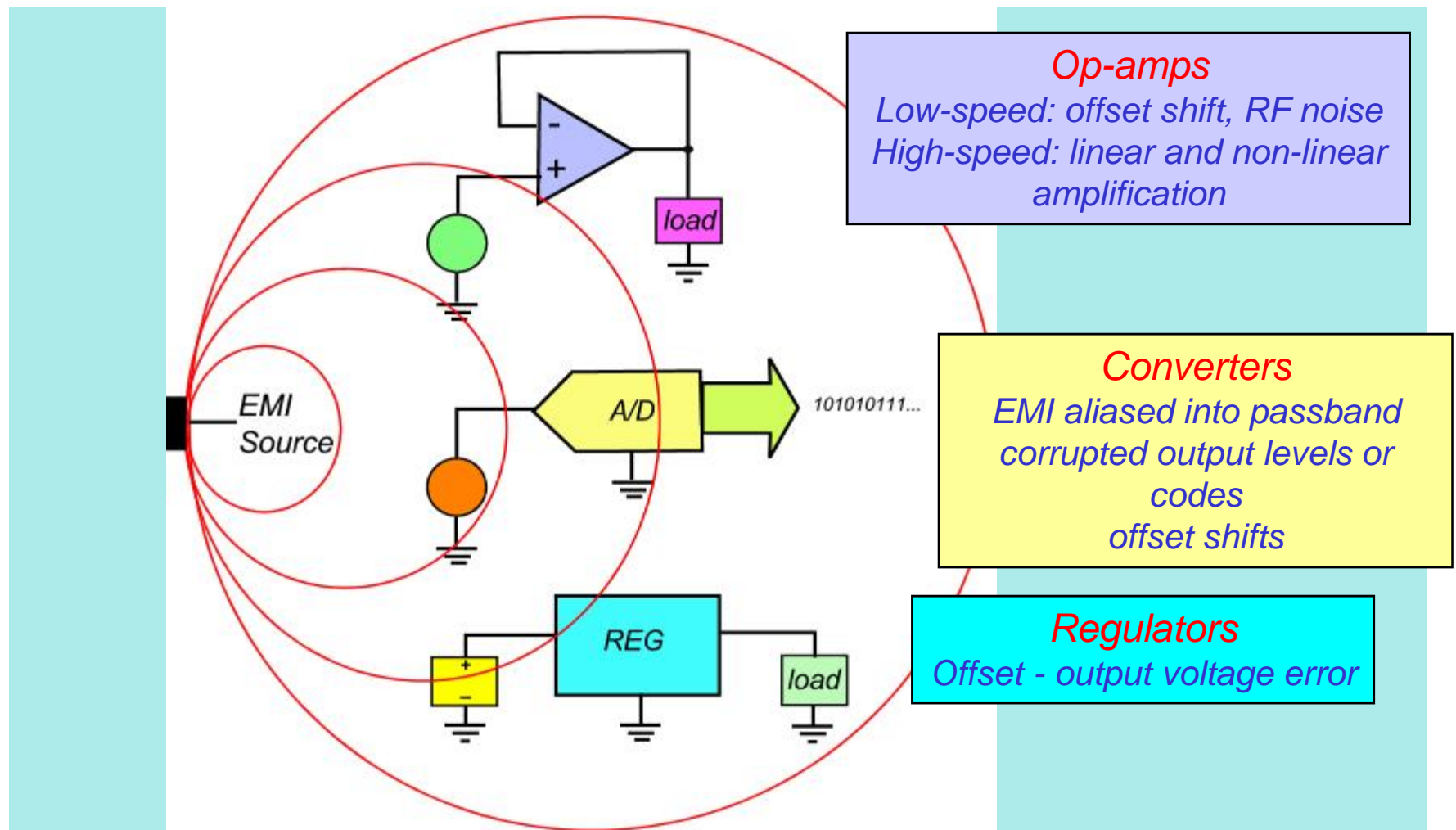


| Freq (MHz) | Class A dBuV/m | Class B dBuV/m |
|------------|----------------|----------------|
| 30 - 80 | 39 | 29.5 |
| 88 - 216 | 43.5 | 33 |
| 216 - 960 | 46.4 | 35.6 |
| 960 - 1000 | 49.5 | 43.5 |

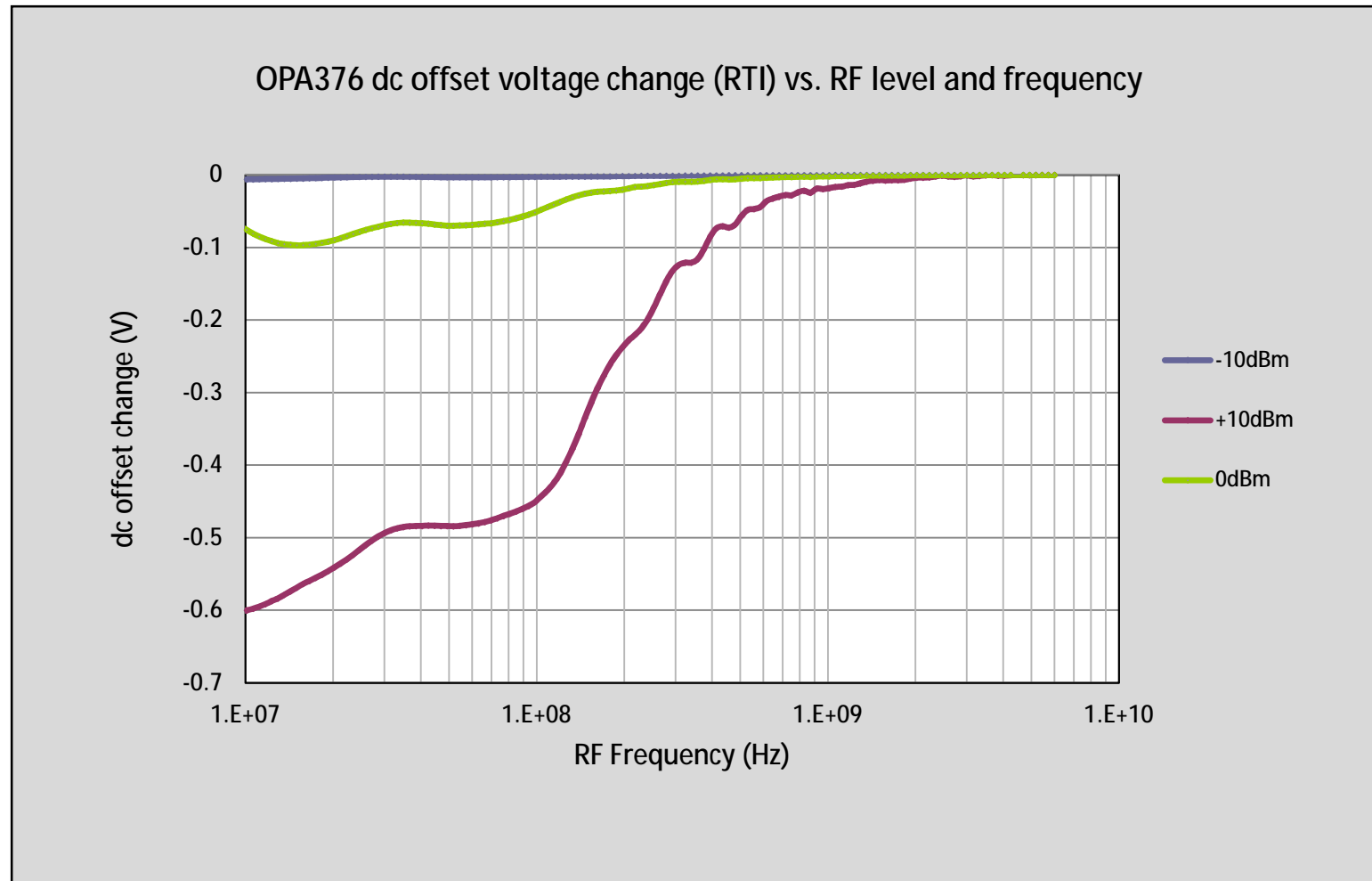
Typical RF field levels



Analog receptors of electromagnetic energy



Operational amplifier voltage-offset shift resulting from conducted RF EMI



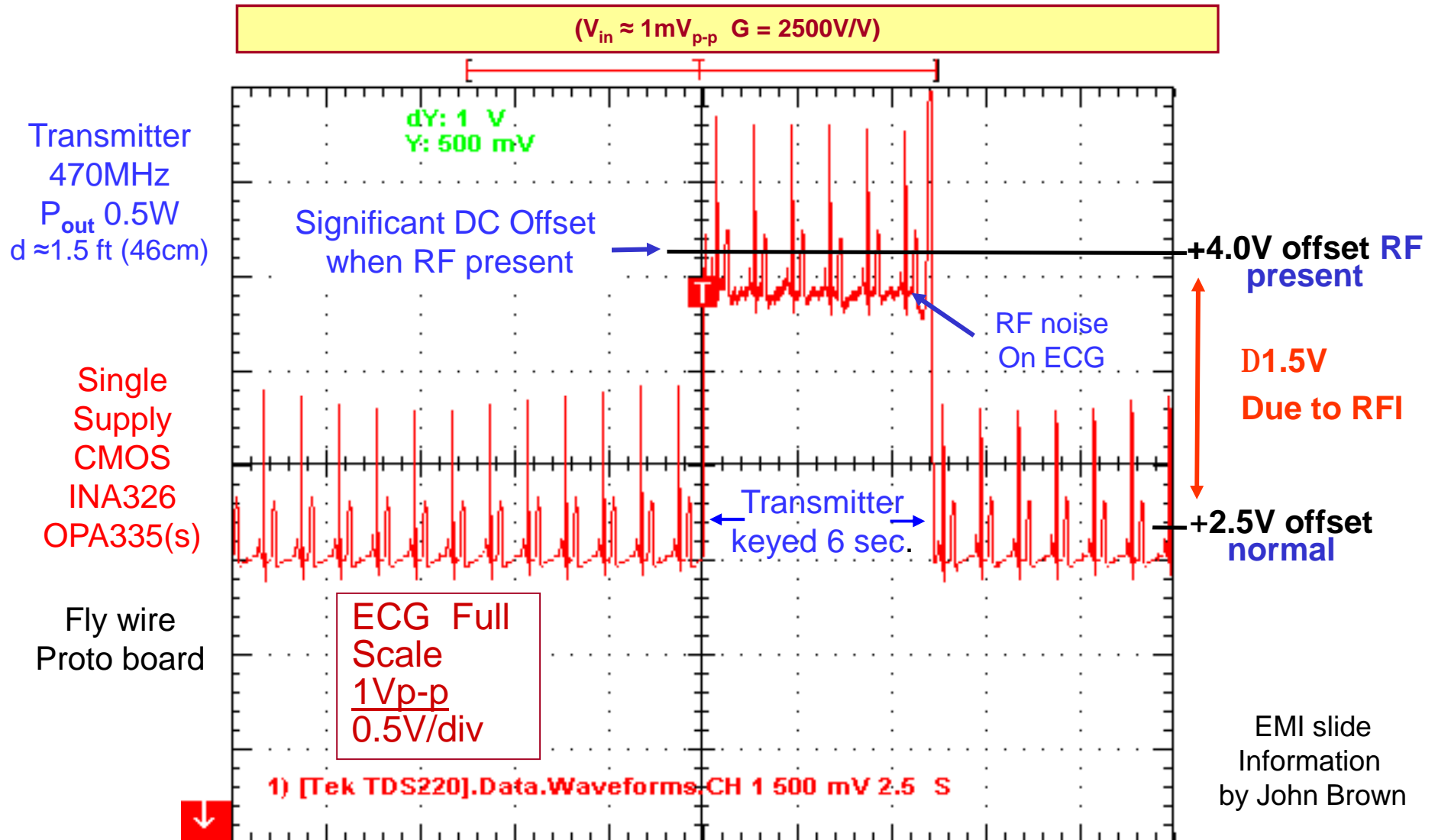
in a 50 Ω system

-10dBm = 100mV_{pk}

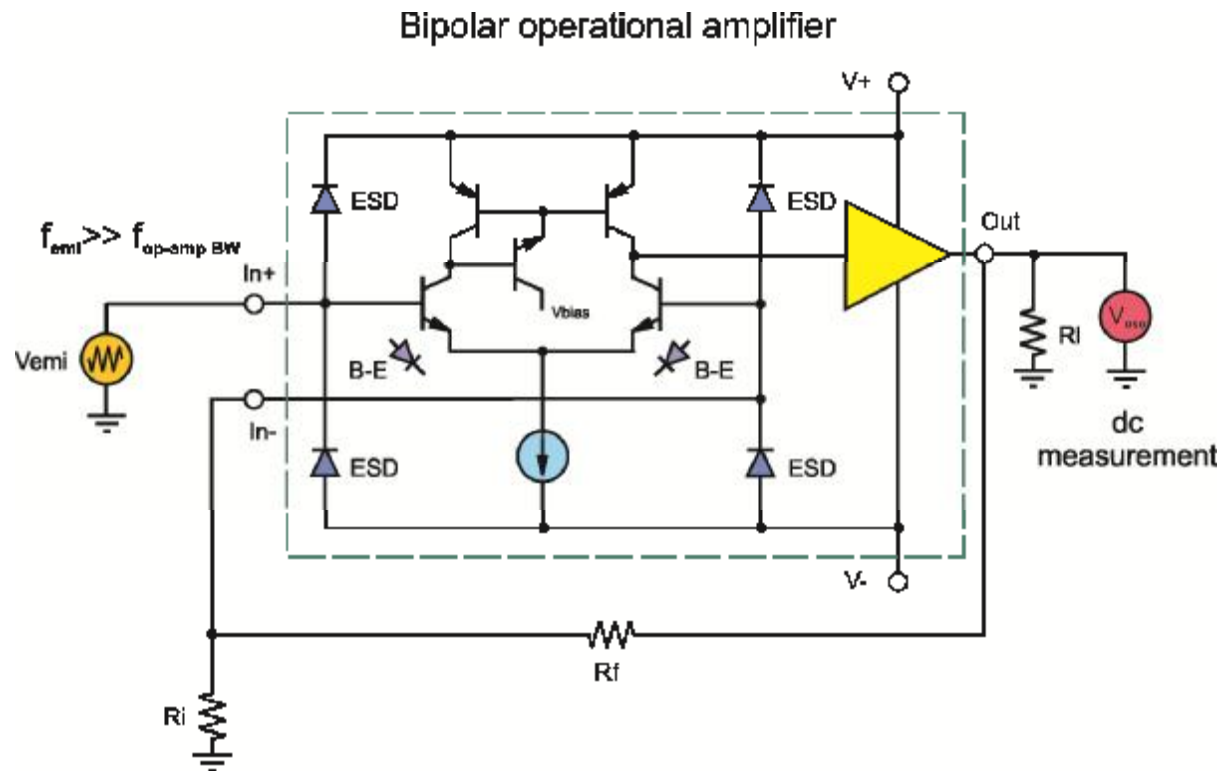
0dBm = 318mV_{pk}

+10dBm = 1.0V_{pk}

Radiated EMI and its affect on an ECG EVM



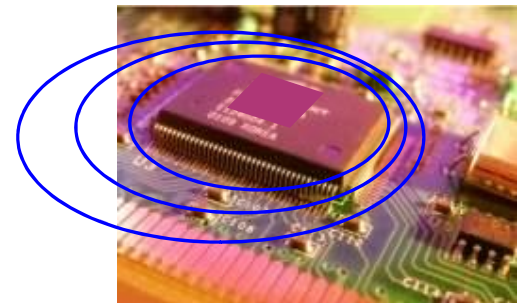
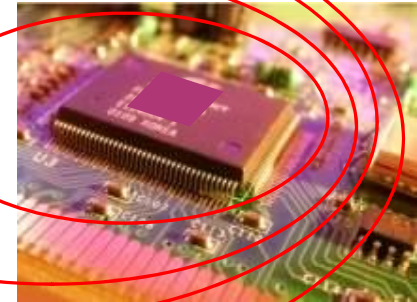
dc rectification by op-amp junctions can produce a voltage offset shift



- Op amp ESD cell and transistor junctions can rectify RFI-EMI
- Resulting dc level is within the bandwidth of the amplifier
- The pulsating dc is filtered by the op-amp bandwidth
- Bandwidth of the op amp is too low to amplify RFI-EMI

Taming the EMI environment

- Minimize EMI radiation from the source
- Reduce the coupling medium's effectiveness
- Reduce receptor circuit's susceptibility to EMI

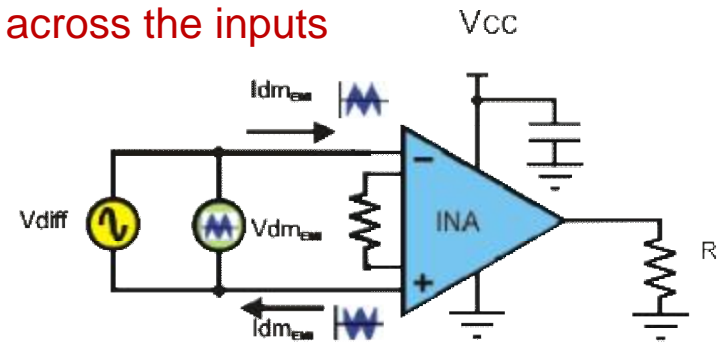


Normal (differential) and common-mode EMI

Normal mode EMI

- normal mode EMI propagates via unintentional loop antennas developed within circuits and wiring
- current level, EMI frequency and loop area determine the antenna's effectiveness
- The EMI induced current is proportional to the loop area

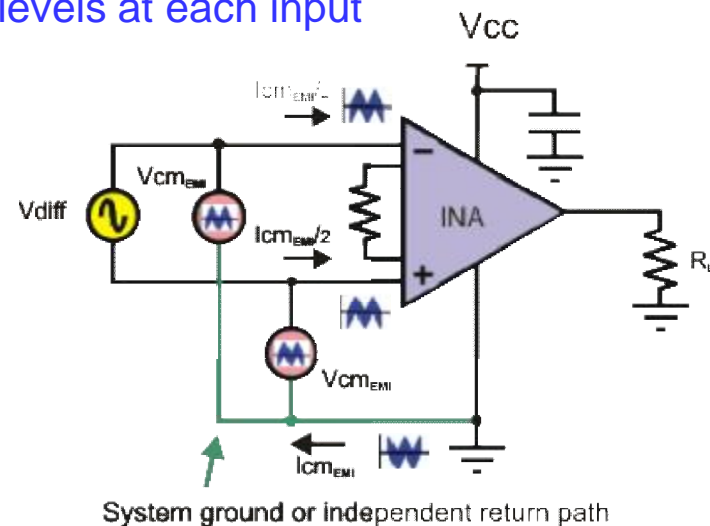
Normal mode EMI appears as a differential signal applied across the inputs



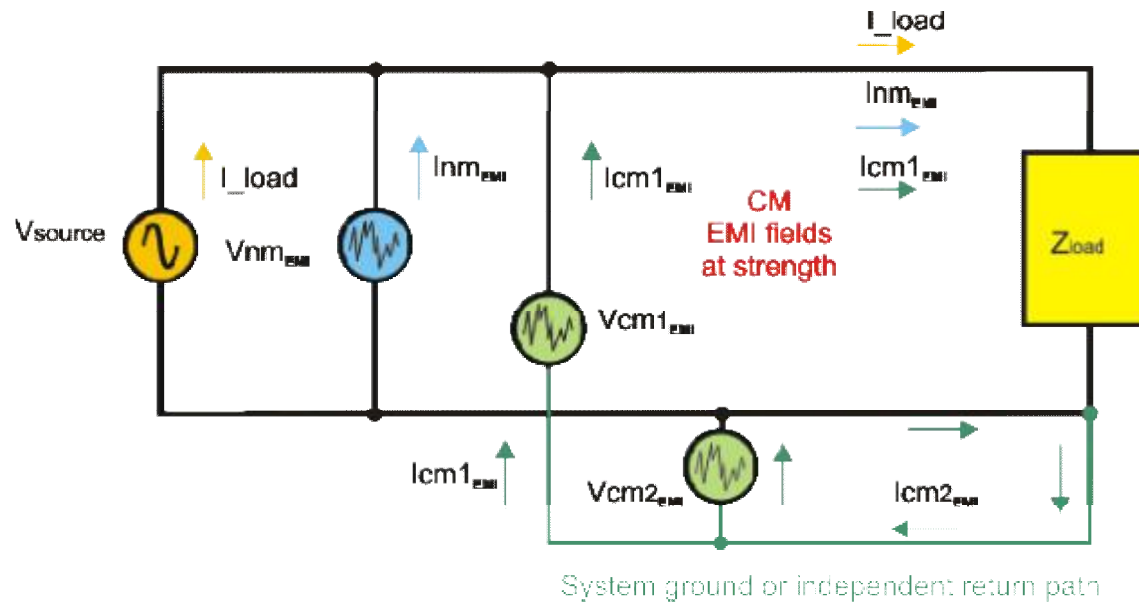
Common-mode EMI

- the majority originates from capacitively coupled (conducted) normal mode EMI
- the higher the frequency the greater the coupling between conductors
- may propagate directly via cabling acting as monopole antennas.
- power chords commonly can act as antennas
- electronic equipment is 10 to 100x more sensitive to common-mode EMI than normal mode EMI

Common-mode EMI produces equal signal levels at each input



Normal and common-mode current flow within a circuit

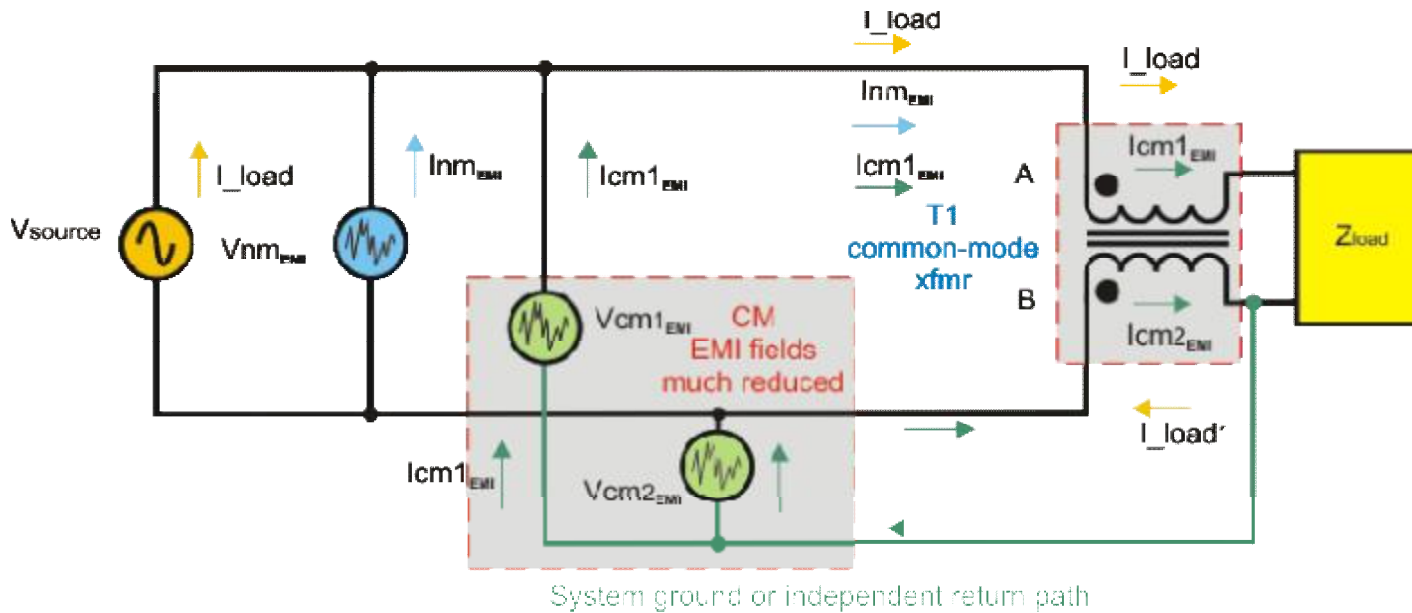


- The load, common-mode EMI current I_{cm1_emi} and normal mode EMI current I_{nm_emi} all flow through the **Zload**
- I_{cm2_emi} circulates through the source return line and the system ground, but not through the **Zload**
- The EMI fields develop at strength and reciprocity is applicable

Basis adopted from Butler Winding, "*Common Mode Choke Theory for Our Custom Built Coils*"

The common-mode transformer

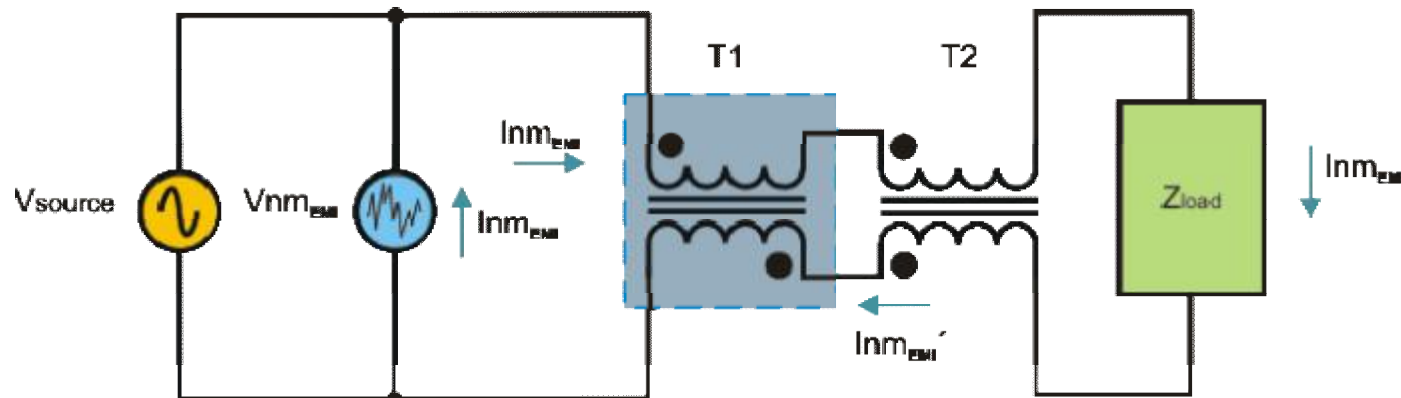
an effective common-mode EMI filter



- The common-mode transformer is a balanced structure having equal turns and winding sense
- The magnetomotive force created by I_{load} is equal and opposite to that created by I_{load}' . Therefore, I_{load} flows through the transformer with no cancelation. This applies to $I_{m_{emi}}$ as well.
- $I_{cm1_{emi}}$ and $I_{cm2_{emi}}$ flow through windings A and B in the same direction and encounter the same level of inductive reactance greatly reducing their amplitude.
- The reduction in $I_{cm_{emi}}$ currents results in a corresponding reduction the EMI fields

Normal mode and common-mode filtering

T1 - normal mode transformer
T2 - common-mode transformer



I_{nm_EMI} and I_{nm_EMI}' encounter
the winding impedance

- The common-mode transformer functions as described previously
- Normal mode EMI cancellation in a specified frequency range may be needed
- The normal mode transformer windings are wound such that normal currents encounter inductive reactance restricting normal model current flow
- Some common-mode transformers are intentionally designed to have high flux leakage inductance. The leakage inductance acts in series with the load providing inductive reactance and normal mode EMI filtering

Common-mode transformer styles

Power line application

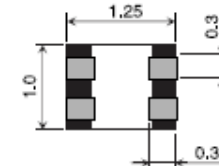


Common Mode Choke

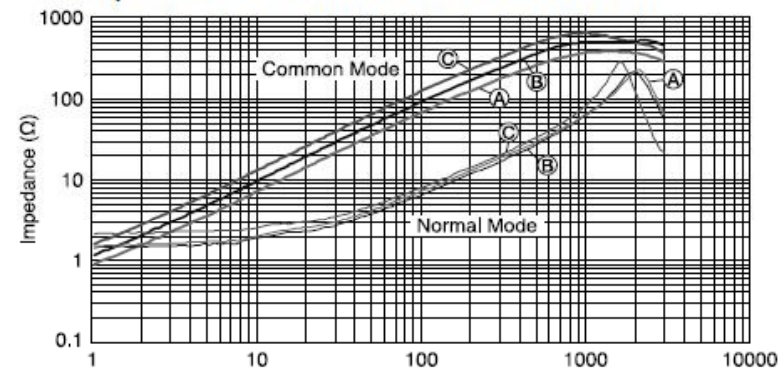
| | |
|----------------------|-----------------------------------|
| Typical Design: | Toroid |
| Core Types: | Toroid, Split Core |
| Core Materials: | Ferrite, Si steel tape wound core |
| AC Current: | Up to 20 Amps, rms |
| DC Current: | Up to 20 Amps |
| Voltage: | Up to 500 Vrms |
| Line Frequency: | Typically 50/60 Hz. |
| EMI Frequency Range: | Application specific |
| Inductance | Application specific |
| Leakage Inductance: | Application specific |
| Hipot | Up to 2,500 Vac, 1-sec |
| Mounting: | Thru Hole, SMT, Bracket |

Signal path application

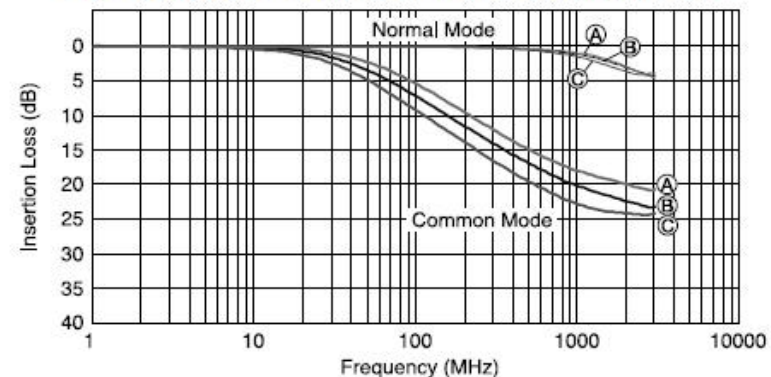
RE TOKO
NTM1210 TYPE



Impedance Characteristics of NTM1210



Insertion Loss Characteristics of NTM1210

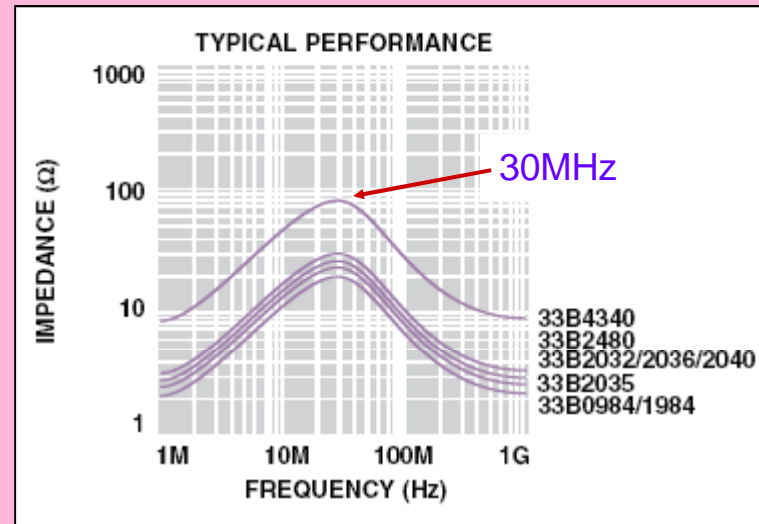


Ferrites for EMI suppression

Ferrite surrounding the cable actually forms a common-mode transformer



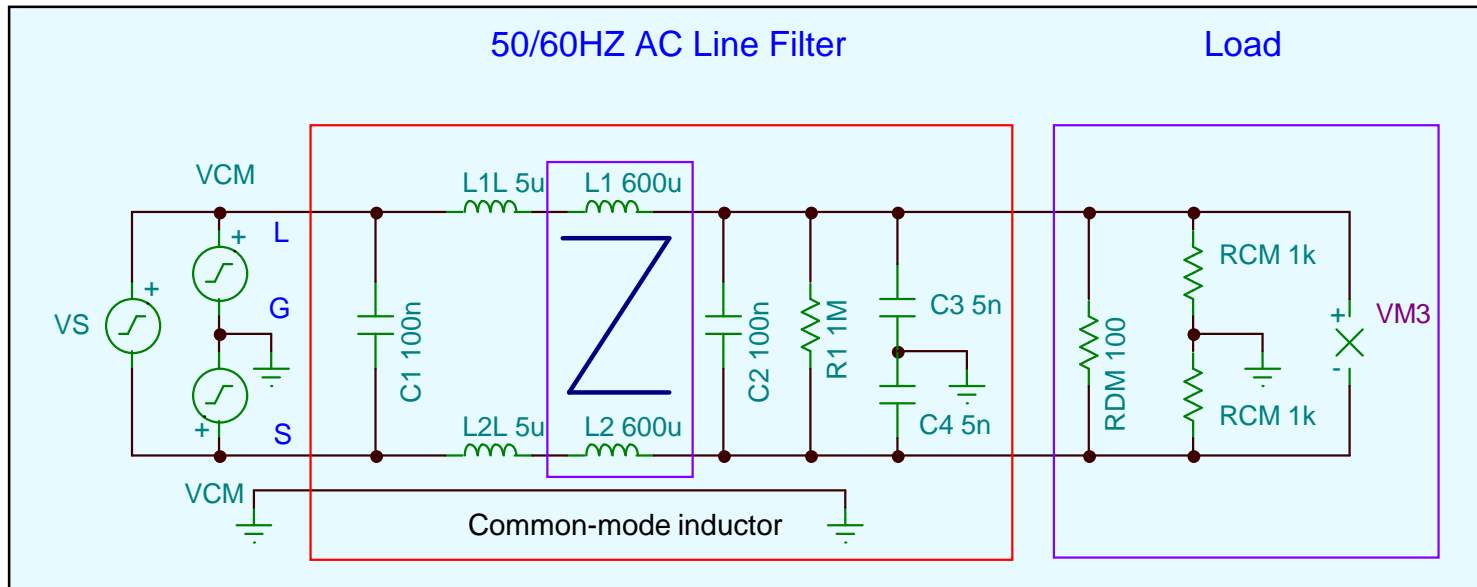
FerriShield[®] INC.
Interference Control Components



Impedance of wire passing through
FerriShield[®] ribbon cable ferrite

Filtering conducted RF-EMI

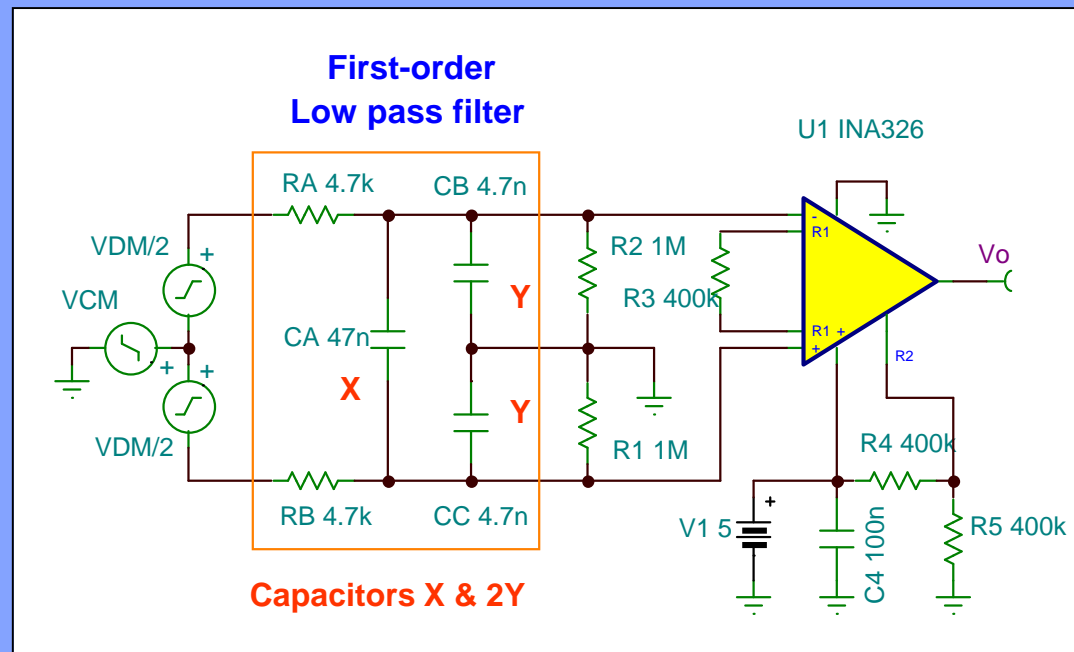
50/60Hz ac line filter example



| Mode | 150kHz | 500kHz | 1MHz | 5MHz | 10MHz | 20MHz | 30MHz | |
|--------------|--------|--------|------|------|-------|-------|-------|----|
| Common | 6 | 20 | 28 | 42 | 45 | 45 | 48 | dB |
| Differential | 10 | 13 | 30 | 50 | 50 | 40 | 40 | dB |

Attenuation characteristics for ac line filter (SAE GA1B-10)

Input RC filtering as applied to an instrumentation amplifier



Differential Mode

$$f_{-3dB} = [2\pi(R_A + R_B)(C_A + C_B/2)]^{-1}$$

$$\text{let } R_B = R_A \text{ and } C_C = C_B$$

$$f_{-3dB} = 343\text{Hz}$$

Common Mode

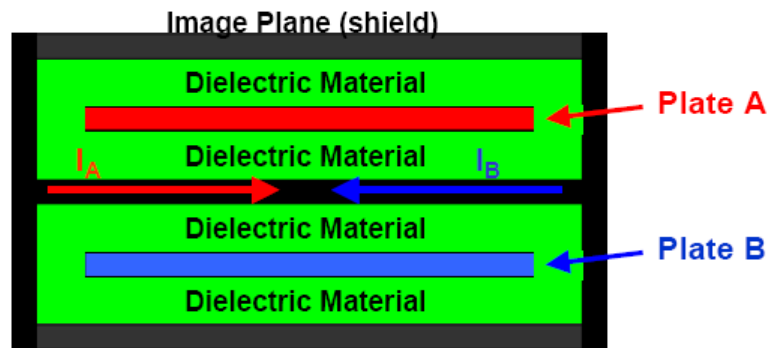
$$f_{-3dB} = [2\pi \cdot R_A \cdot C_B]^{-1}$$

$$\text{let } R_B = R_A \text{ and } C_C = C_B$$

$$f_{-3dB} = 7.2\text{kHz}$$

X2Y[®] Capacitor Architecture

X2Y Architecture

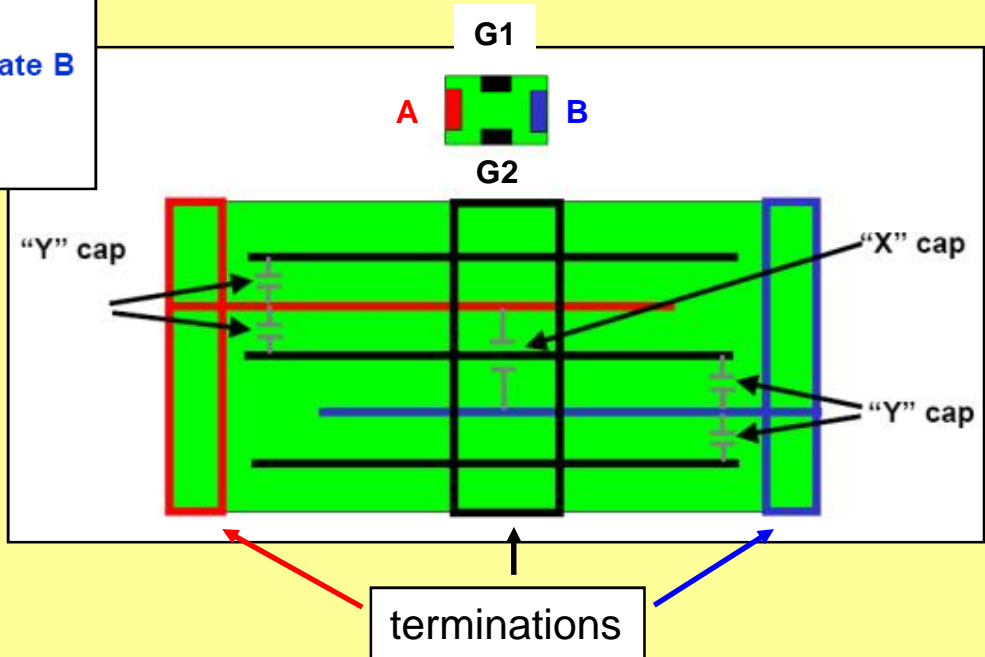


$$C_x = \frac{1}{2} C_y$$

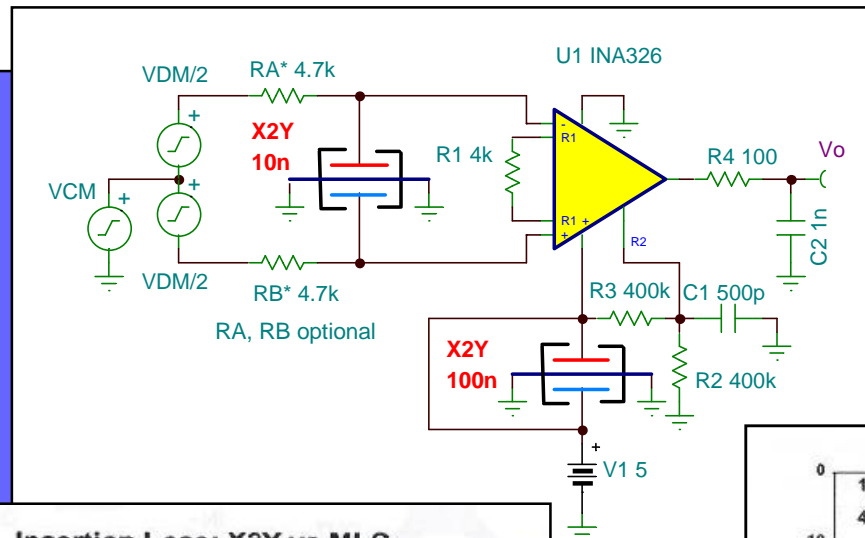
From Yageo.com website

The X2Y capacitor

- 1 'X' capacitor, 2 'Y' capacitors
- Effective for both common-mode and differential-mode filtering
- Excellent capacitance matching



The X2Y[®] capacitor in application

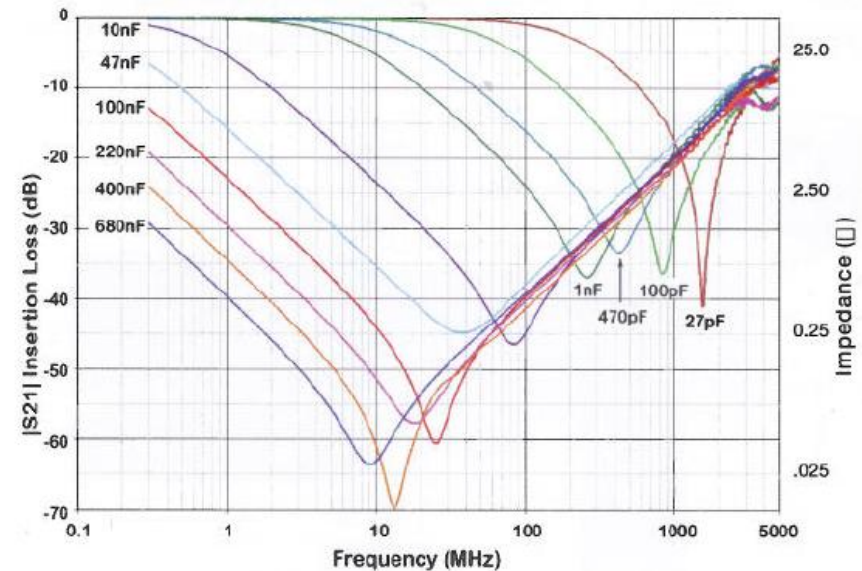
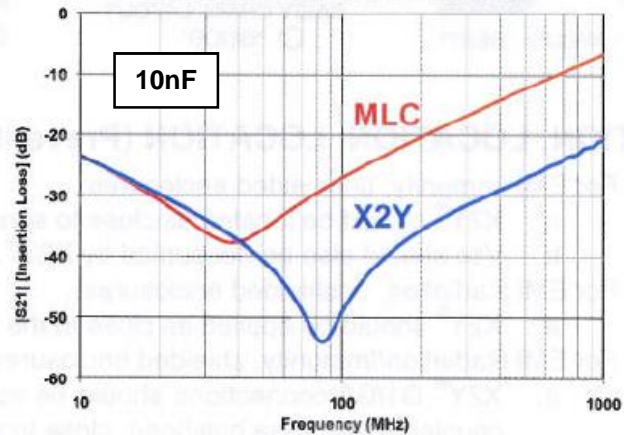


JOHANSON DIELECTRICS

X2Y[®] Filter & Decoupling Capacitors

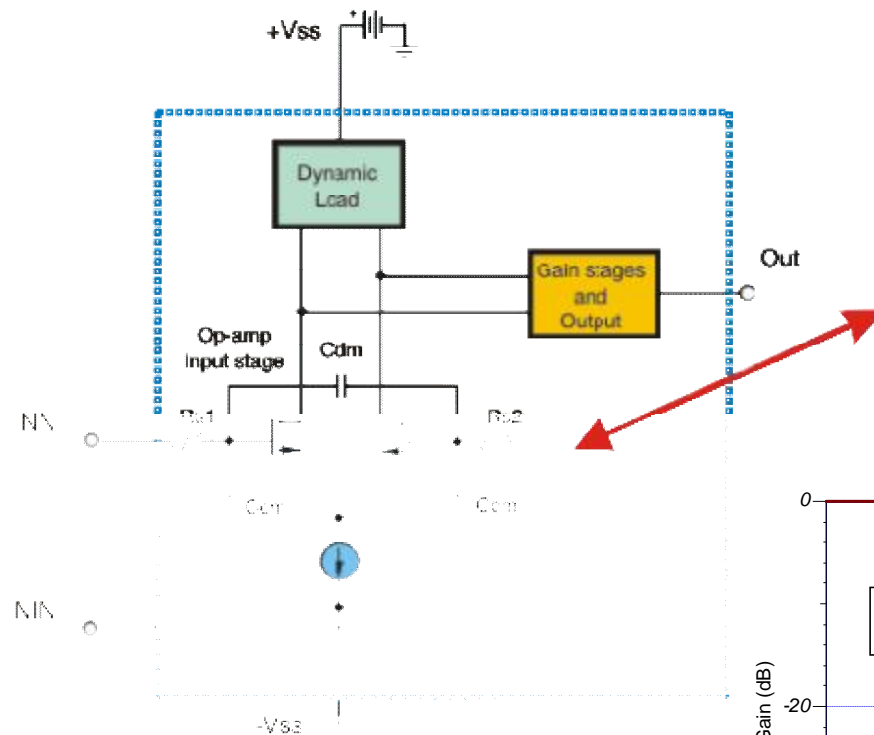
Input filtering s21
Signal-to-Ground

Insertion Loss: X2Y vs MLC

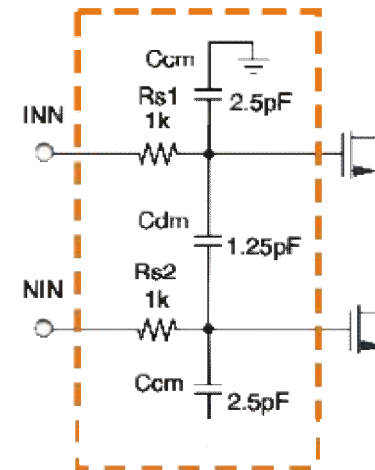


Newer op-amps have built-in EMI filtering

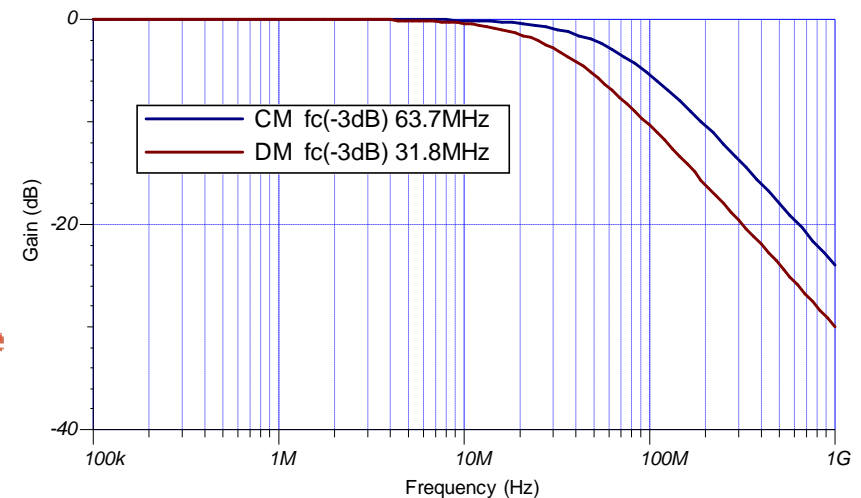
Simplified CMOS Op-amp



Built-in input EMI Filter

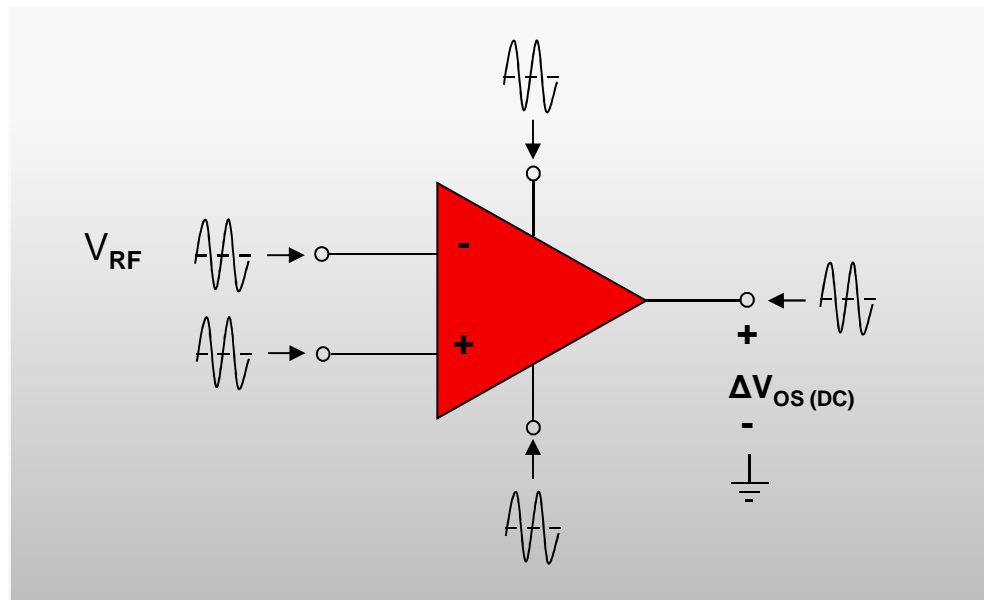


Filter response



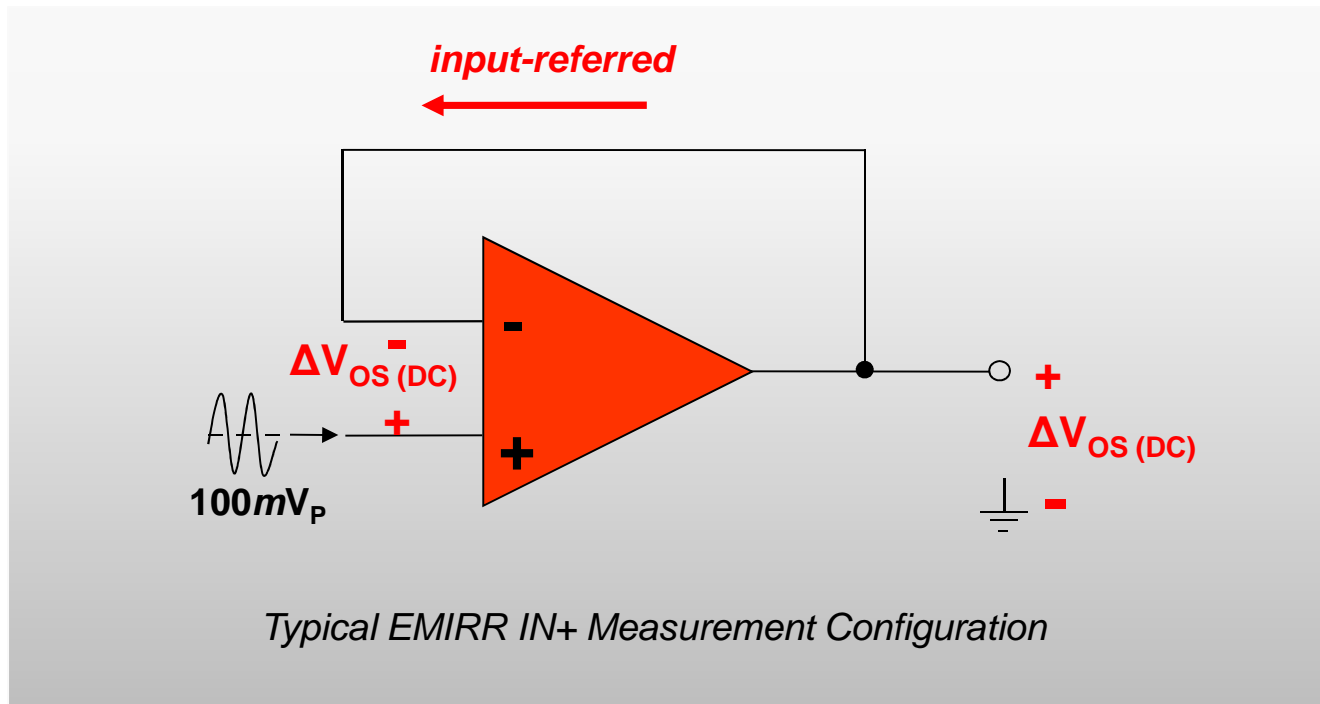
EMIRR- a measure quantifying an operational amplifier's ability to reject EMI

- EMIRR – Electromagnetic Interference Rejection Ratio
- Defined in National Semiconductor's application note AN-1698
- Measured as a dB voltage ratio of output offset voltage change in response to an injected RF voltage having a defined level
- Provides a definitive measure of EMI rejection across frequency allowing for a direct comparison of the EMI susceptibility of different operational amplifiers



EMIRR IN+

- EMI testing of operational amplifier pin functions has shown that the input pins are the most sensitive to EMI and produce the largest offset shift
- EMIRR IN+ is the EMI rejection ratio of the non-inverting input. The term EMIRR IN+ has become nearly synonymous with EMIRR
- The operational amplifier is connected as a unity-gain buffer during the test. An RF signal with a specified drive level is applied to the non-inverting input



EMIRR IN+ equation

$$EMIRR\ IN^+ \ (dB) = 20 \cdot \log \left(\frac{V_{RF_PEAK}}{|\Delta V_{OS}|} \right) + 20 \cdot \log \left(\frac{V_{RF_PEAK}}{100mV_P} \right)$$

- V_{RF_PEAK} = peak amplitude of the applied RF signal @ op-amp input
- ΔV_{OS} = resulting “input-referred” DC offset voltage shift @ op-amp output
- $100mV_P$ = standard EMIRR input level (-10 dBm)

Higher EMIRR IN+ equates to lower amplifier EMI sensitivity

EMIRR IN+ equation solved for $|\Delta V_{OS}|$

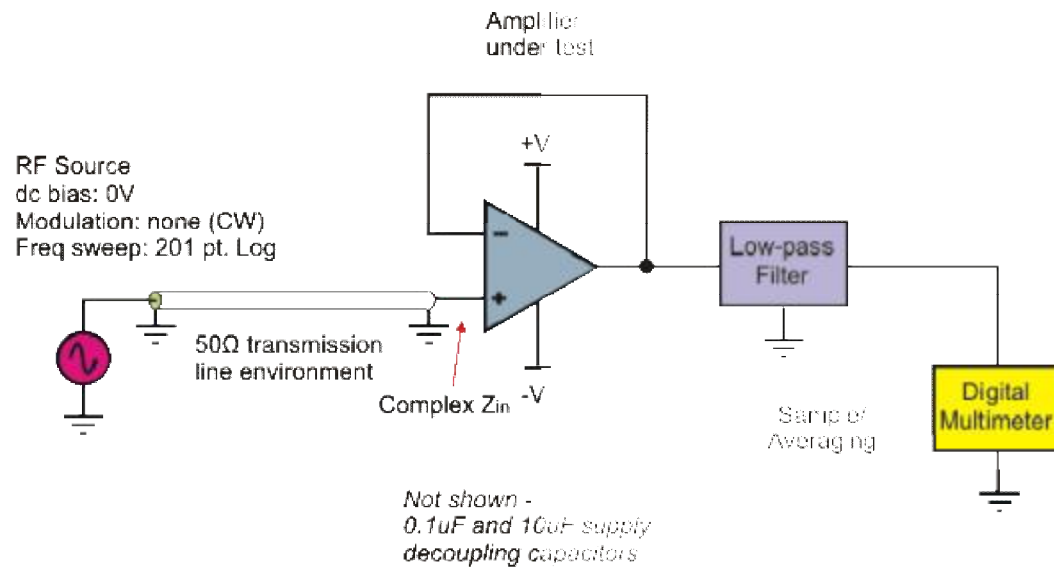
$$|\Delta V_{OS}| = \frac{1}{10^{\left(\frac{EMIRR\ IN+(dB)}{20}\right)}} \cdot \left(\frac{V_{RF_PEAK}^2}{100mV_P} \right)$$

- Use this equation to solve for $|\Delta V_{OS}|$ of a unity gain amplifier if V_{RF_PEAK} and EMIRR IN+ are known such as when a plot is provided
- EMIRR IN+ is frequency dependant
- **Doubling V_{RF_PEAK} Quadruples $|\Delta V_{OS}|$!**
- For example: 100mV_P RF signal at 1.8GHz produces an EMIRR IN+ of 60 dB. The associated voltage offset shift would be 100uV

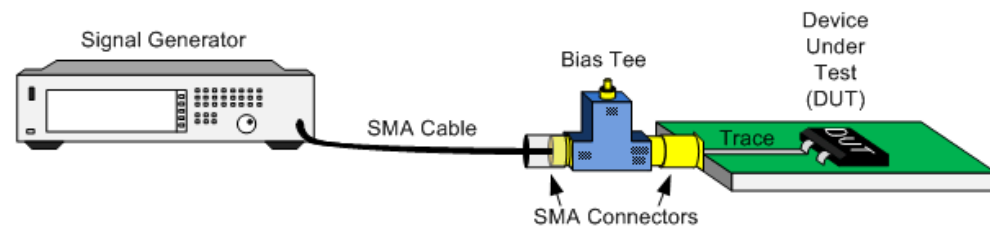
The EMIRR IN+ test set-up

See TI Application Report SBOA128 for details

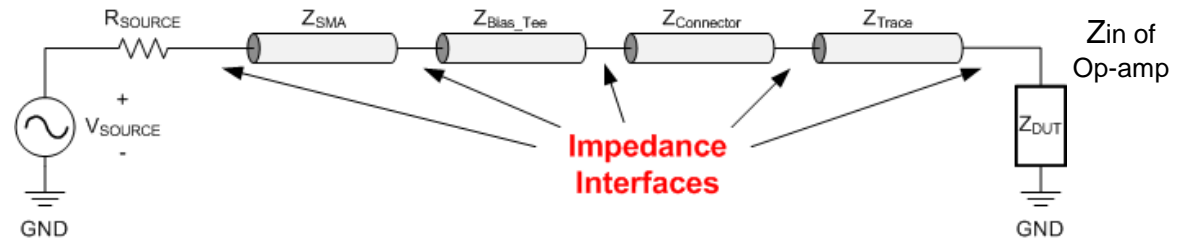
Simple schematic for EMIRR IN+ test



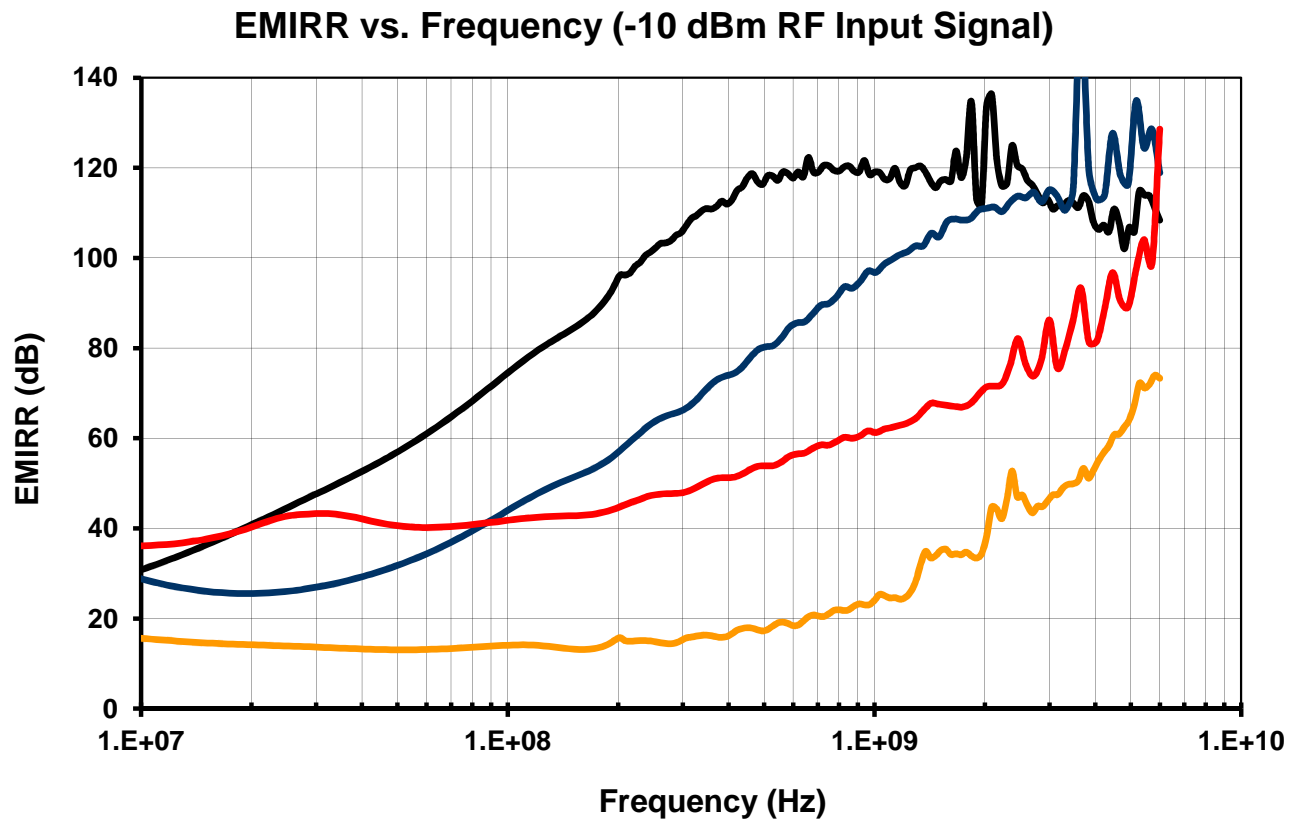
Practical implementation



The complex RF input environment



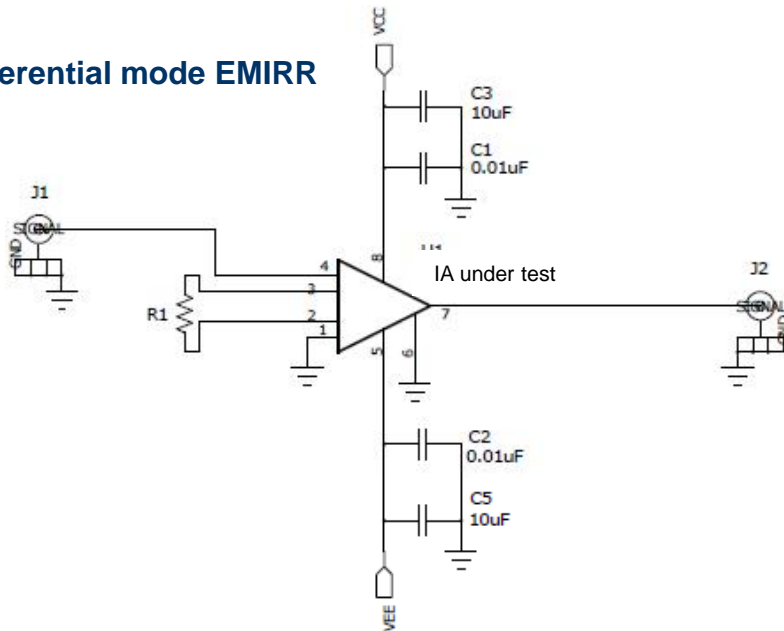
EMIRR IN+ measurement results for TI CMOS rail-to-rail operational amplifiers



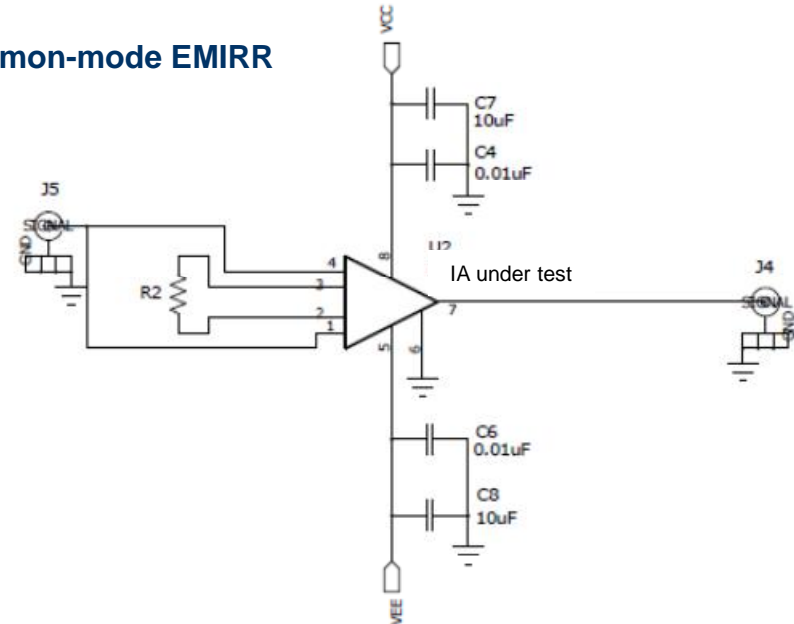
| Model | GBW | Filter | Model | GBW | Filter |
|-------------|--------|--------|-------------|--------|--------|
| OPA333/2333 | 350kHz | Yes | OPA376/377 | 5.5MHz | Yes |
| OPA378 | 500kHz | Yes | OPA348/2348 | 1MHz | No |

EMIRR testing applied to instrumentation amplifiers

Differential mode EMIRR



Common-mode EMIRR



Test Configuration

Bipolar supplies (+/-V), reference pin grounded, RF level -10dBm

Differential measurement

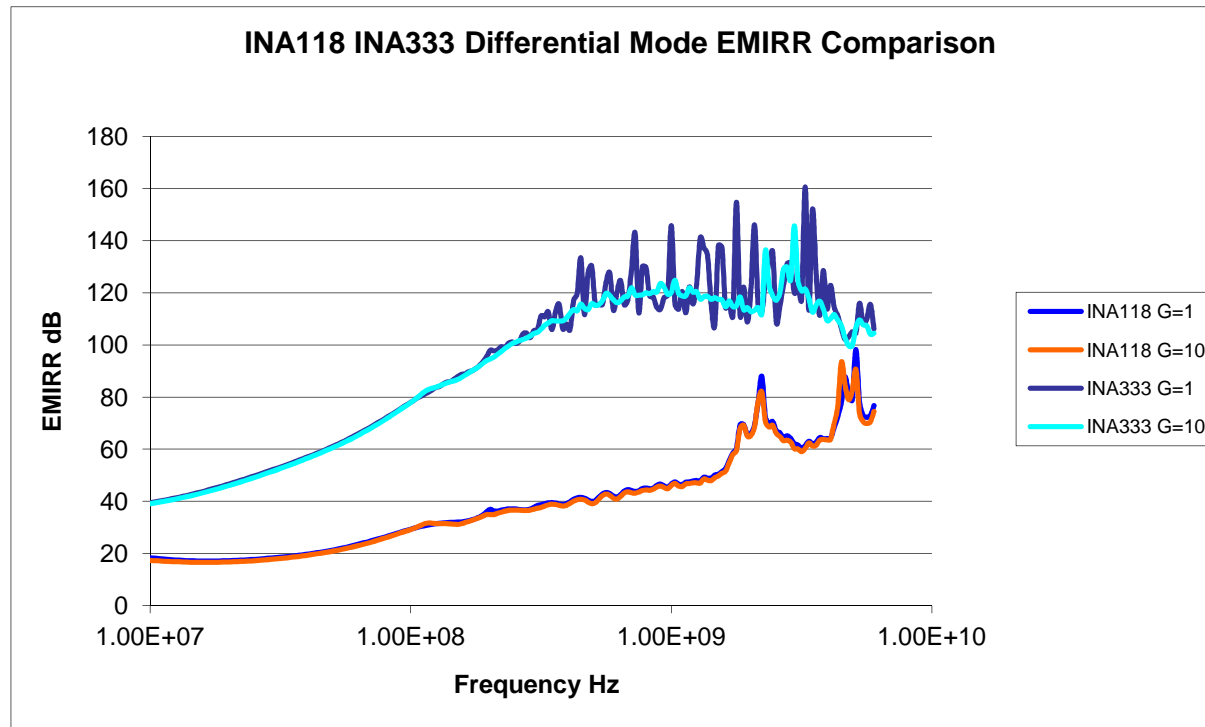
- RF signal applied to non-inverting input
- Inverting input grounded

Common-mode Measurement

- RF signal applied to both inputs

EMIRR testing applied to instrumentation amplifiers

INA118 – INA333 differential mode comparison



INA118

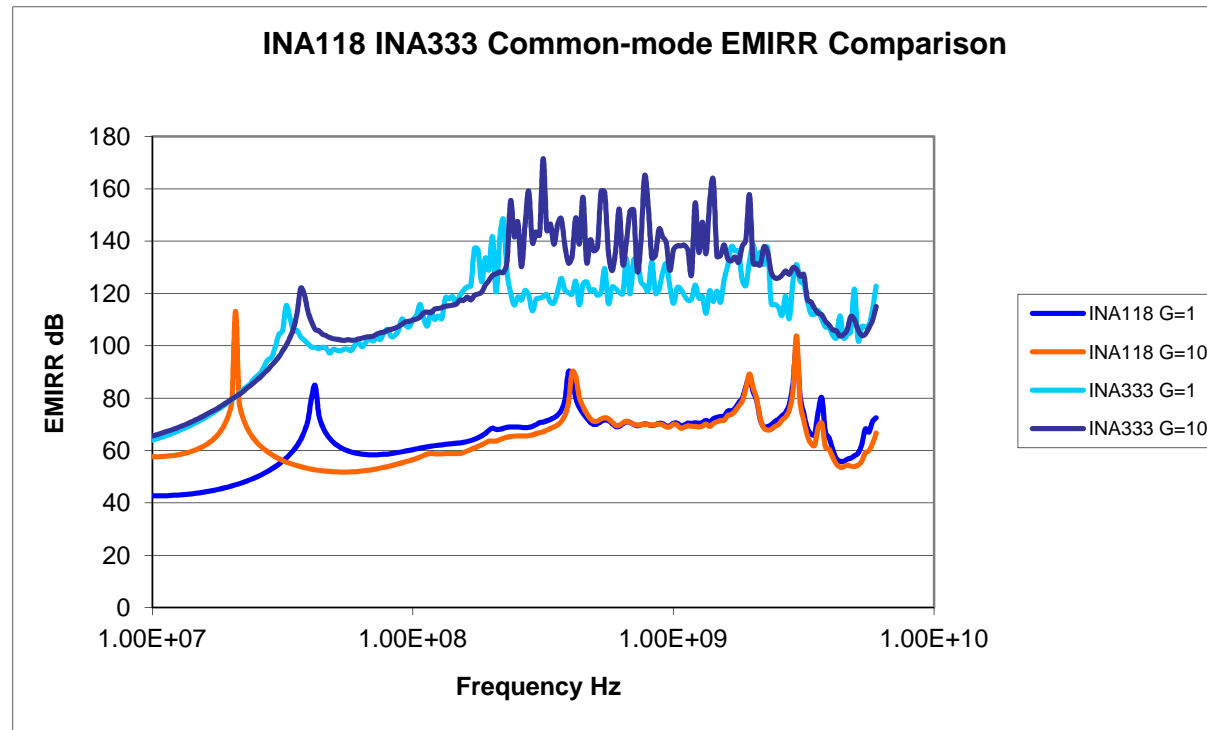
- 3 op-amp current feedback design
- A_v range 1 to 10kV/V
- 70kHz BW, $G = 10V/V$
- I_q 350uA
- circa 1994
- no internal EMI filter

INA333

- 3 op-amp CMOS auto-zero design
- A_v range 1 to 1kV/V
- 35kHz BW, $G = 10V/V$
- I_q 50uA
- 2008 introduction
- internal EMI filter

EMIRR testing applied to instrumentation amplifiers

INA118 – INA333 **common-mode** comparison



INA118

- 3 op-amp current feedback design
- A_v range 1 to 10kV/V
- 70kHz BW, $G = 10V/V$
- I_q 350uA
- 1994 introduction
- no internal EMI filter

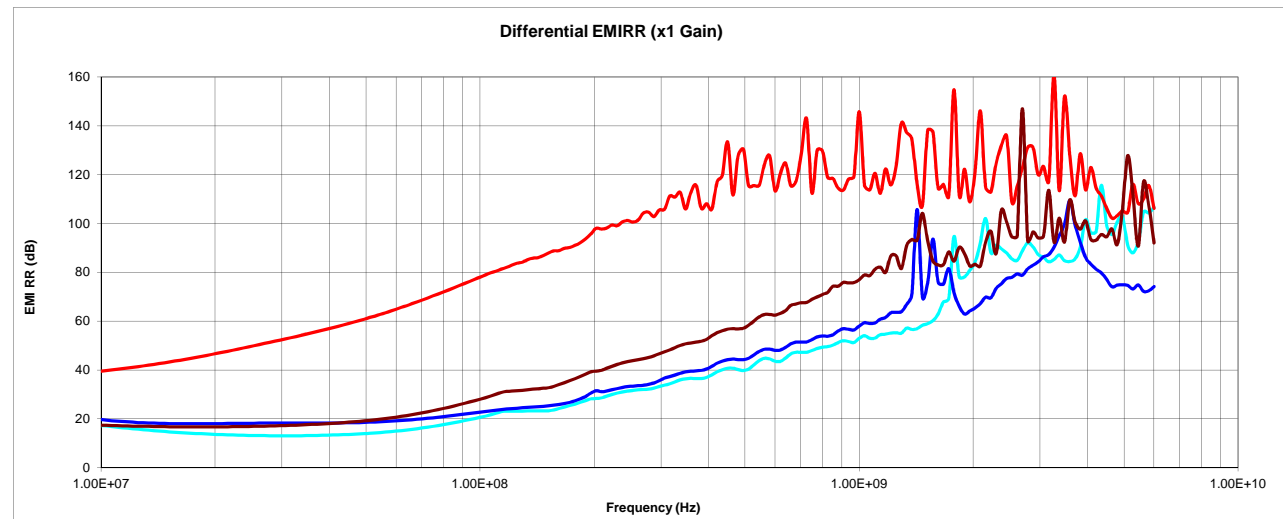
INA333

- 3 op-amp CMOS auto-zero design
- A_v range 1 to 1kV/V
- 35kHz BW, $G = 10V/V$
- I_q 50uA
- 2008 introduction
- internal EMI filter

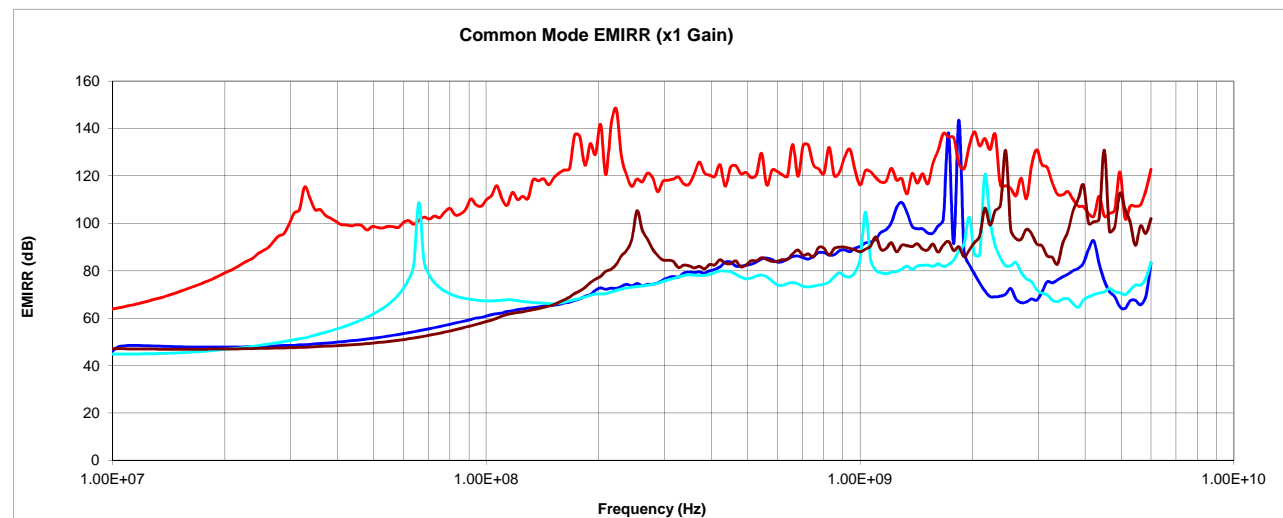
Instrumentation amplifier EMIRR performance comparison

- TI - INA333
- competitor A
- competitor B
- competitor C

Differential mode EMIRR

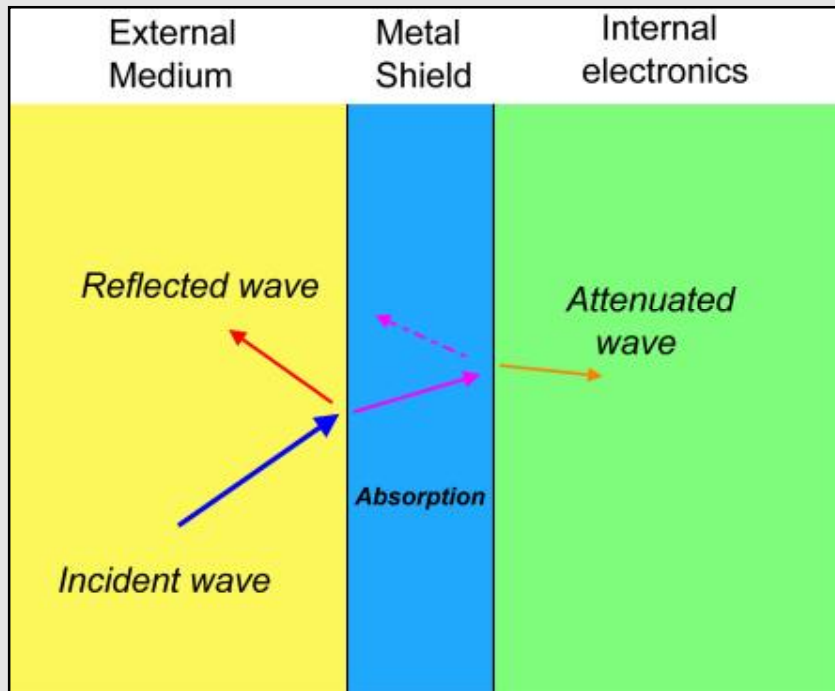


Common-mode EMIRR



Shielding and screening

Minimizing the medium's effectiveness



Derived from: *EDN – The Designer's Guide to Electromagnetic Compatibility*

Shielding Effectiveness (S.E.) of enclosed material

Emission Suppression

$$S.E._{dB} \text{ (Em. Supp.)} \approx A_{dB}$$

Susceptibility

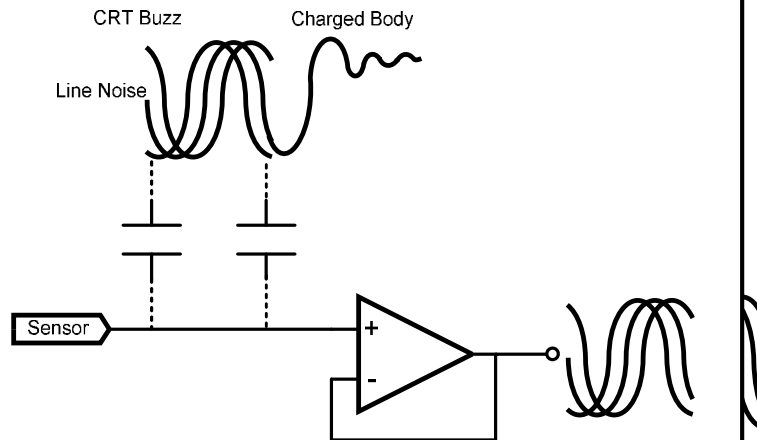
$$S.E._{dB} \text{ (Sus.)} \approx A_{dB} + R_{dB} \text{ (appropriate)}$$

where: A: absorption loss in dB
R: reflection loss in dB

From: COTS Journal, January 2004 – “Design Considerations In Building Shielded Enclosures.”

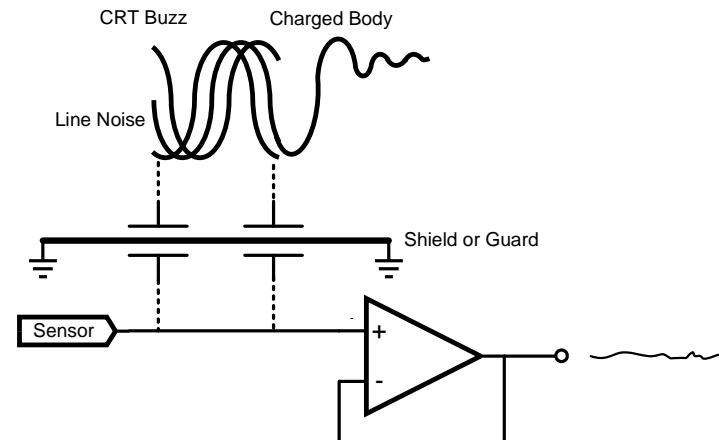
Noisy Neighbors - Electrostatic Noise

Without Shield



- Noise is capacitively coupled into high impedance node
- $I = C * (\Delta V / \Delta T)$
- Changing capacitance (distance) or voltage creates a current
- Circuit can “see” you moving
- Vibrations create ΔC

With Shield



- Inserting a “plate” between the two plates breaks the field path.
- Plate does not have to be ferrous, just conductive (aluminum).

Shielding and screening

Minimizing medium's effectiveness

Metal Shielding

Magnetic field $f < 20\text{kHz}$

Ferrous metals

- steel
- Mu-metal – nickel, iron

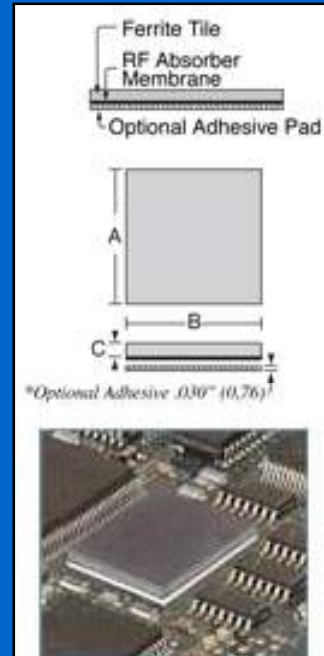
RF fields $10\text{kHz} < f < 1\text{GHz}$

Non-ferrous metals

- Al foil $I_{\text{Loss}} > 90\text{dB}$
- Cu, Ni $I_{\text{Loss}} 40\text{-}60\text{dB}$
- Vacuum plating
 $I_{\text{Loss}} > 80\text{dB}$
- Electroless deposition
 $I_{\text{Loss}} > 80\text{dB}$

From: EDN EMI/EMC guide

Ferrite shield



RF absorber shield



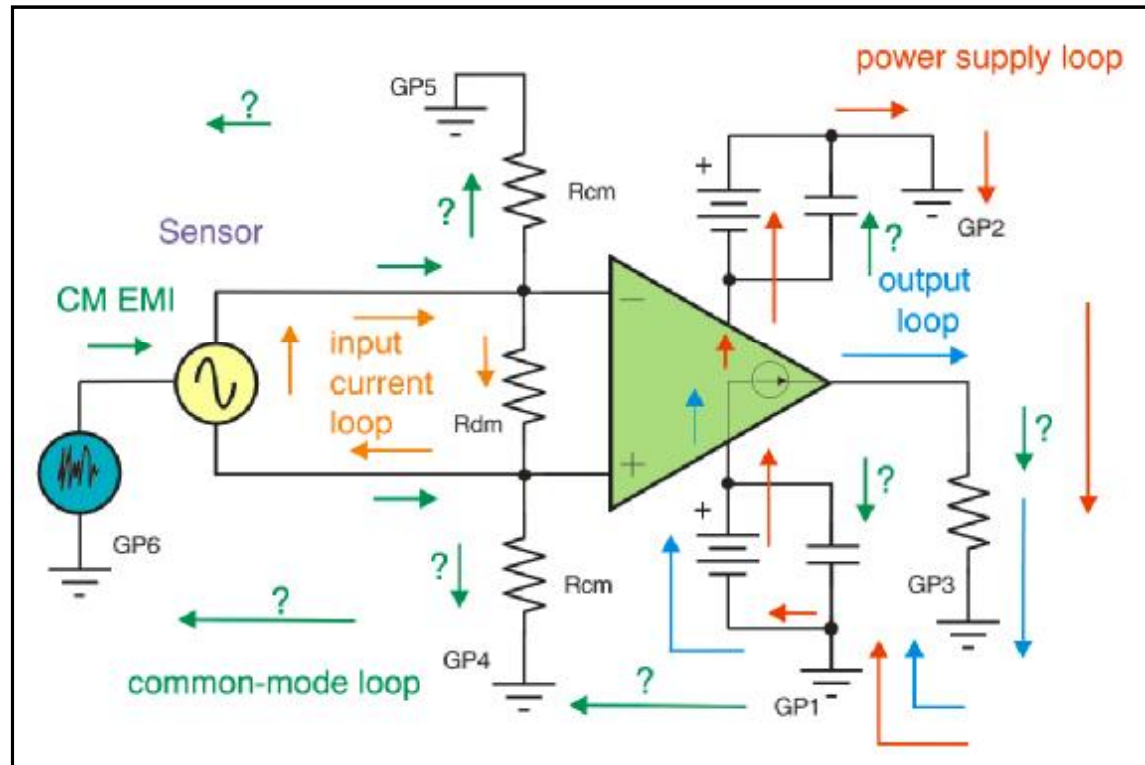
FerriShield[®] INC.
Interference Control Components

A loop – the path current follows

Loops

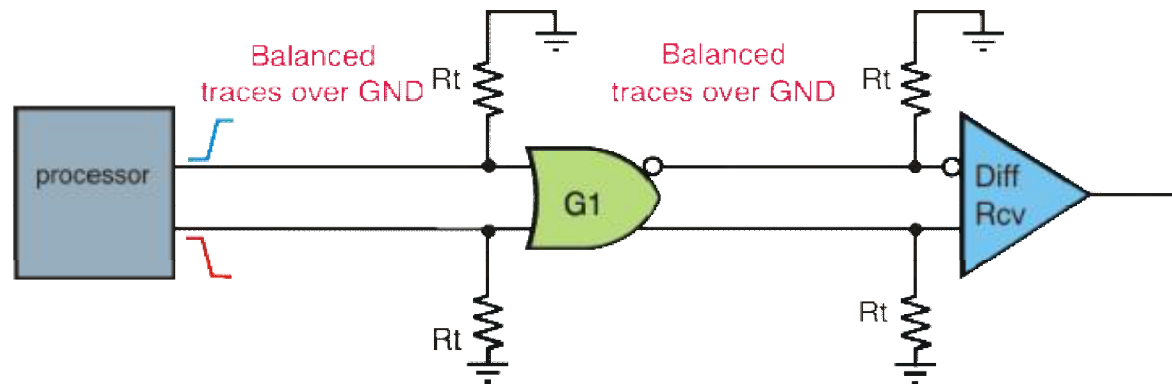
- dc, ac and EMI signal may share loop paths
- EMI-RFI will take the path of least impedance
- The current loop may act as a loop antenna coupling EMI/RFI in, or out, of the circuit

The common-mode return loop may be difficult to predict

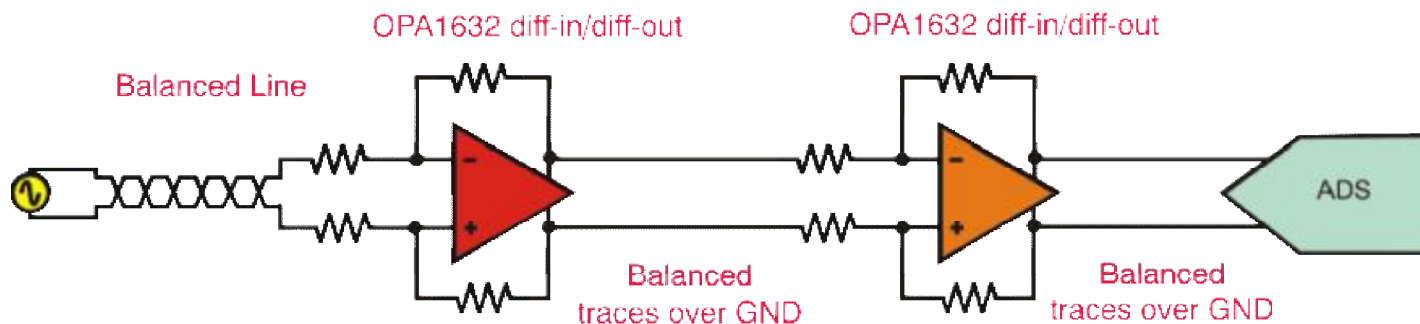


Balanced analog and digital circuitry reduces common-mode response

Balanced digital logic: LVDS, PECL, HSTL



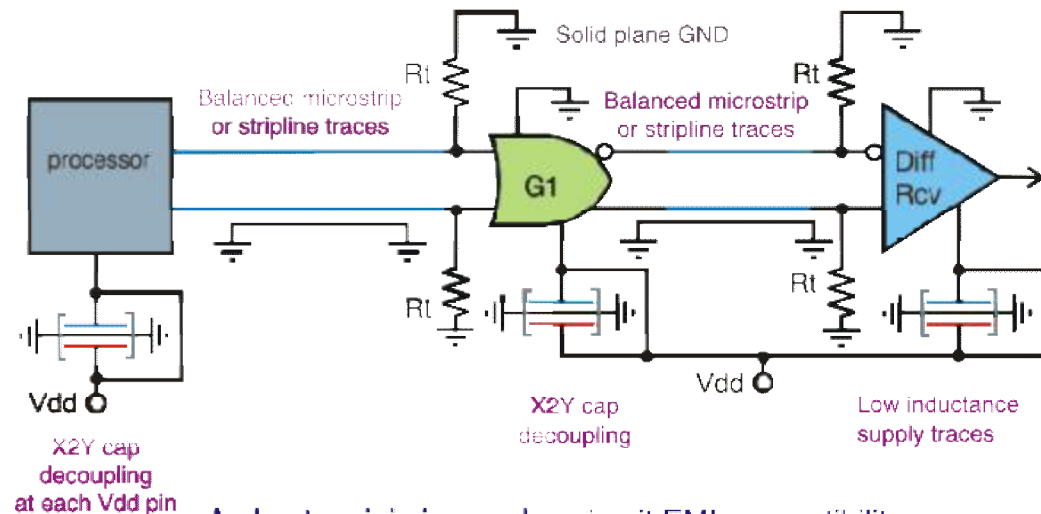
Balanced differential analog circuitry



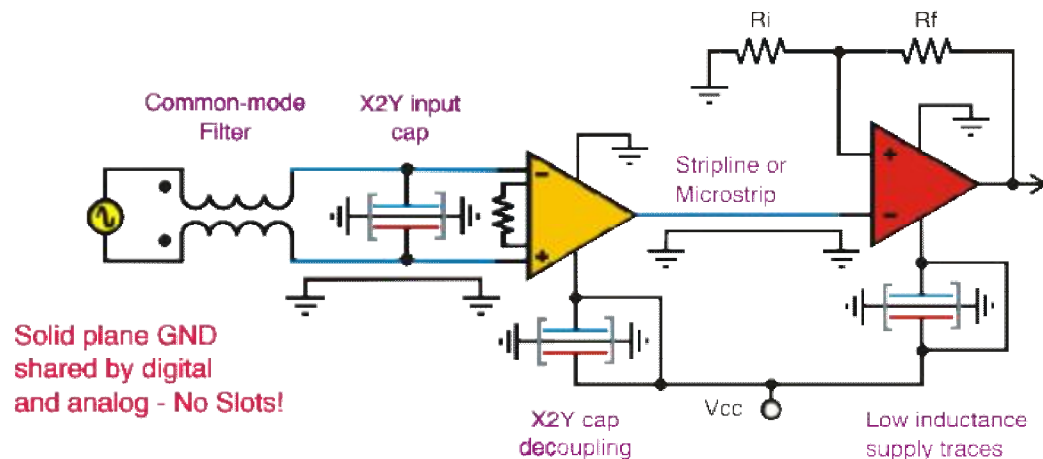
Circuit plans to help minimize EMI

- Strive for a zero impedance ground
- Design for a differential signal environment, both logic and analog
- Minimize PCB loops that act as EMI antennas
- Use X2Y capacitors for filtering and decoupling
- Make use of common-mode transformers
- Use balanced lines and traces

A plan to reduce digital circuit EMI generation



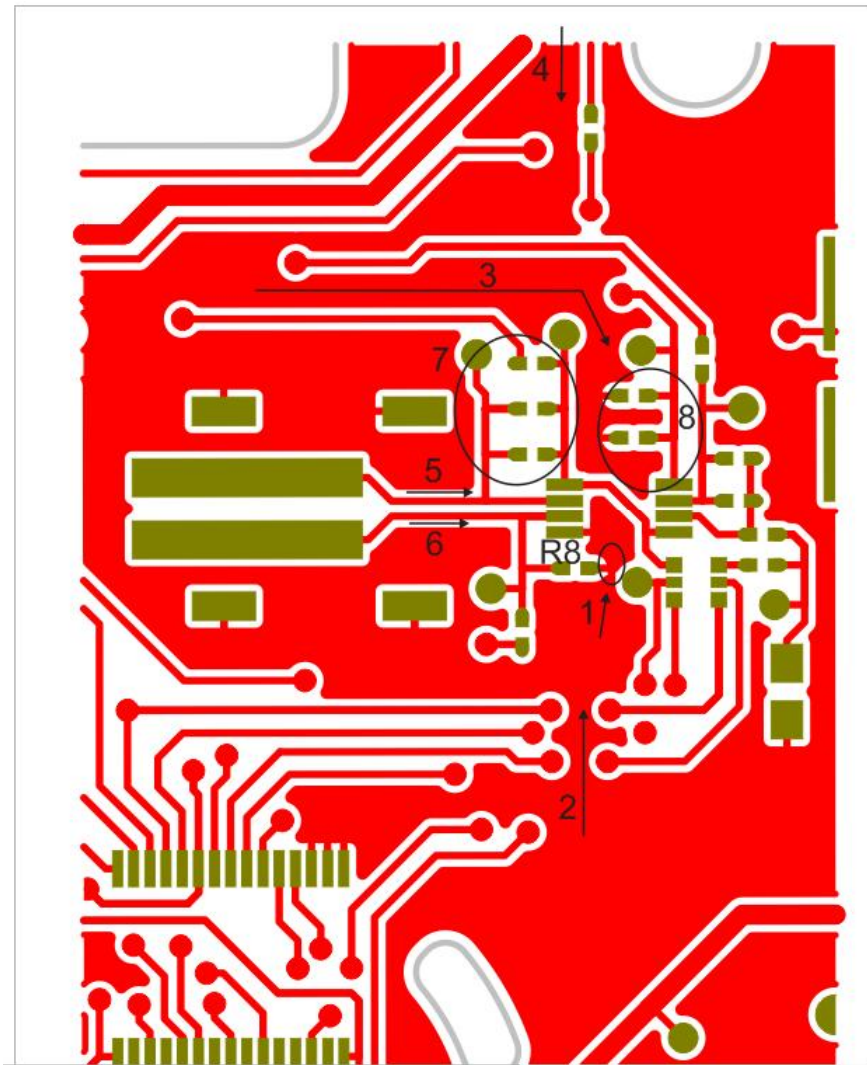
A plan to minimize analog circuit EMI susceptibility



PC board tips to help reduce EMI's affect in circuits

- Minimize path inductance, especially ground which may be the return for many signals.
- Use a continuous ground plane. Avoid slots in the plane. They increase path length increasing the inductance.
- Place potential EMI sources on one end of board, potential receptors on the other end.
- Extend balanced line concepts to the board; especially, in the low-level signal circuits.

A PB board that failed radiated EMI testing in several hundred MHz range



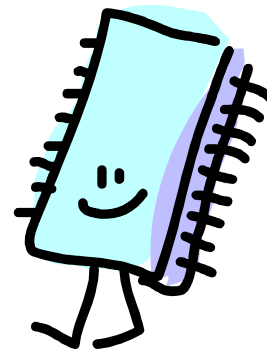
Board layout includes TI dual CMOS op amp

- 1-4 - long ground return paths increases return impedance and loop areas
- 5,6 – long, unbalanced input traces
- 7, 8 – Decoupling capacitors are too distant and have long traces
- No ground plane!
- RFI – EMI performance likely wasn't considered during board layout

In conclusion EMI/RFI

- May constitute an operational, regulatory or liability concern
- Is best considered as part of the design process
- Requires a source, medium and receptor
- Propagates by conduction and/or radiation
- Most often appears as a dc offset shift in precision linear circuits
- Can most often be resolved by reducing the effectiveness of an EMI source or medium and responsiveness of a receptor circuit

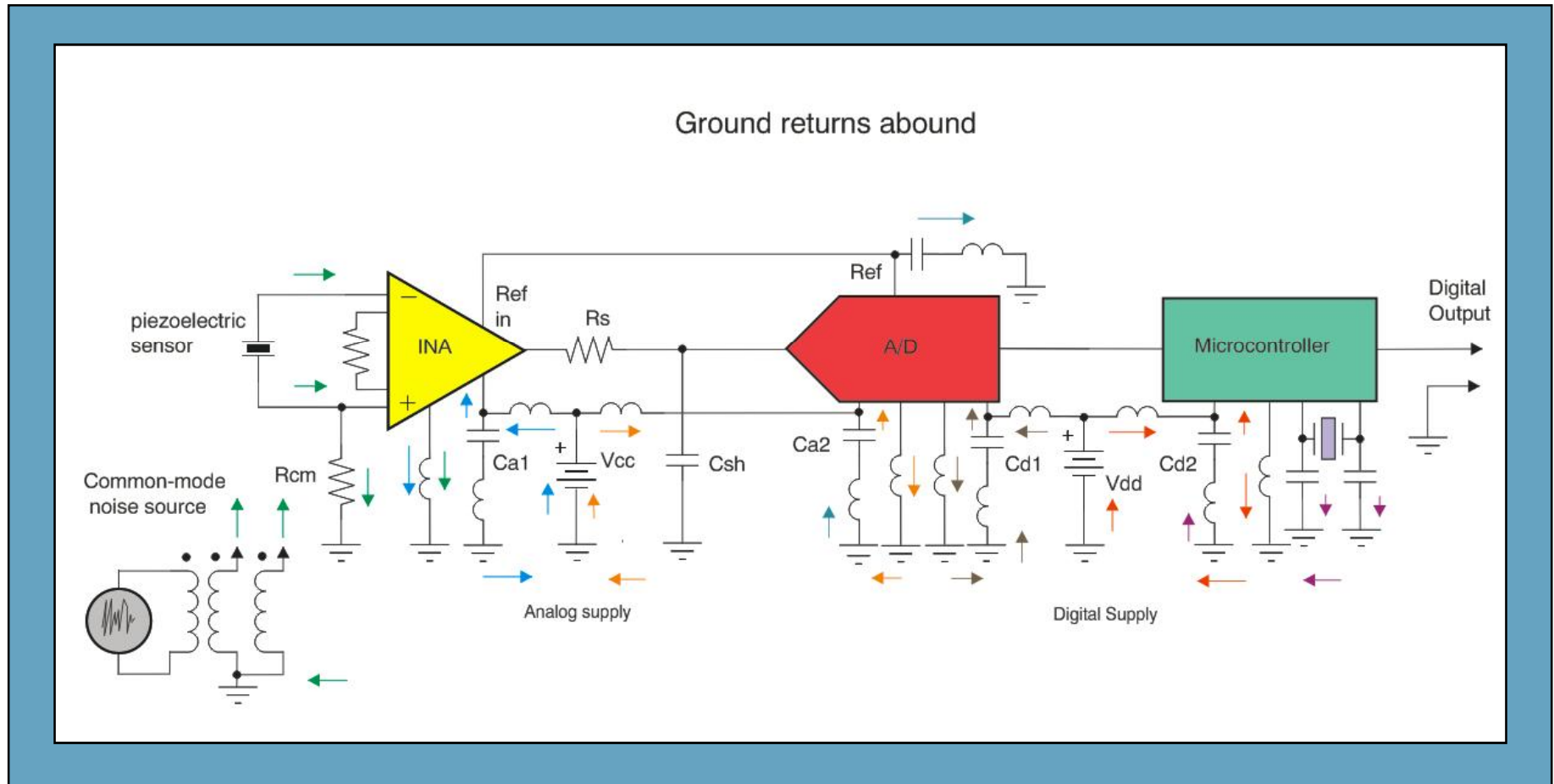
A happy IC - EMI free!



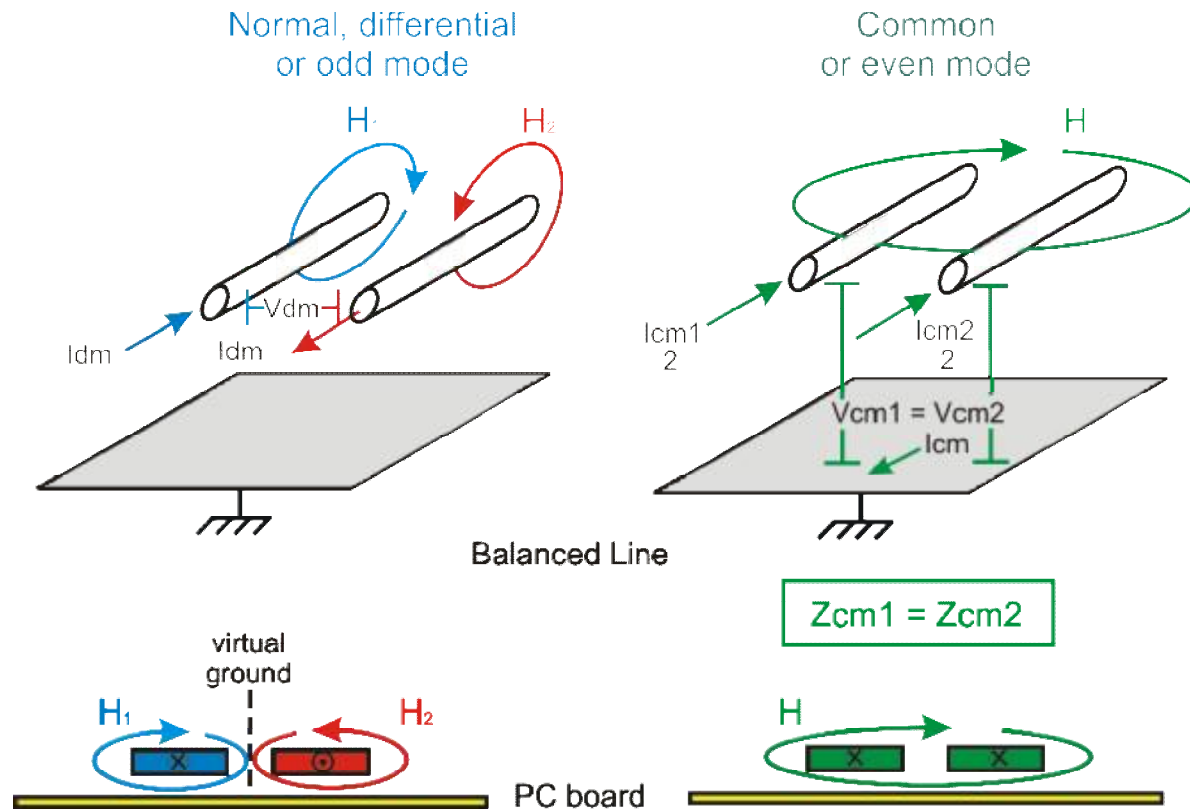
Appendix

The ground return environment may be complex

Current paths must be carefully considered to avoid long loops



Balanced line helps keep induced common-mode EMI from differential conversion



- balanced line presents induced EMI as an equal level, same phase signal to amplifier input
- the common-mode rejection of the amplifier or transformer will act upon the common-mode EMI
- twisting the line improves balance by equalizing the field exposure of both wires